

Supplementary Materials

Dialkylboryl-Substituted Cyclic Disilenes Synthesized by Desilylation-Borylation of Trimethylsilyl-Substituted Disilenes

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1. NMR Spectra

Boryldisilene 3

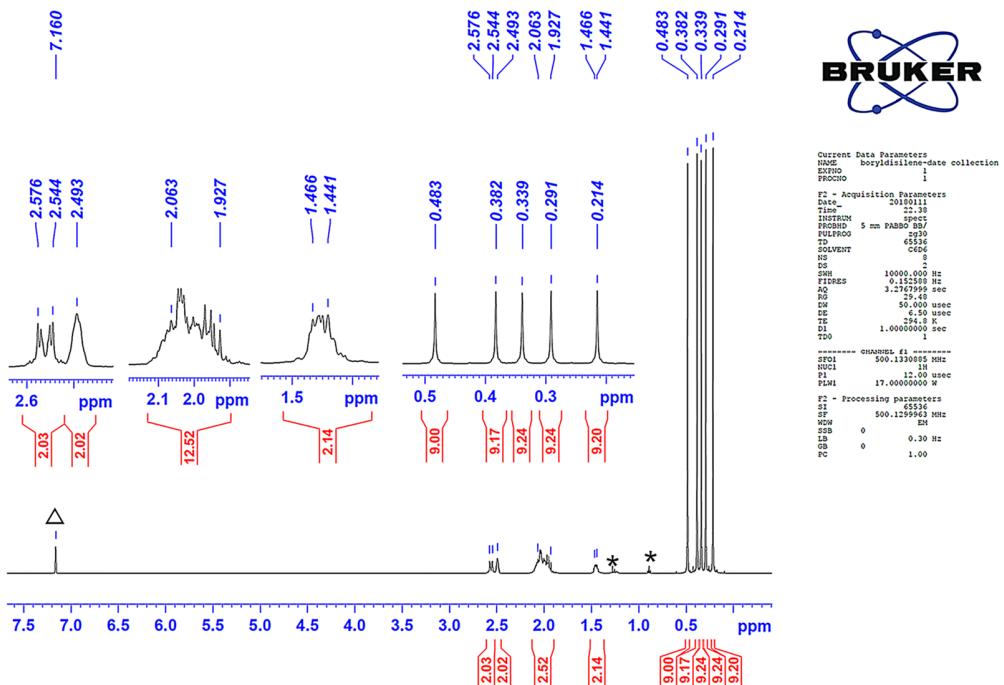


Figure S1. ^1H NMR spectrum of **3** in C_6D_6 at 295 K ($\triangle = \text{C}_6\text{D}_5\text{H}$, * = hexane).

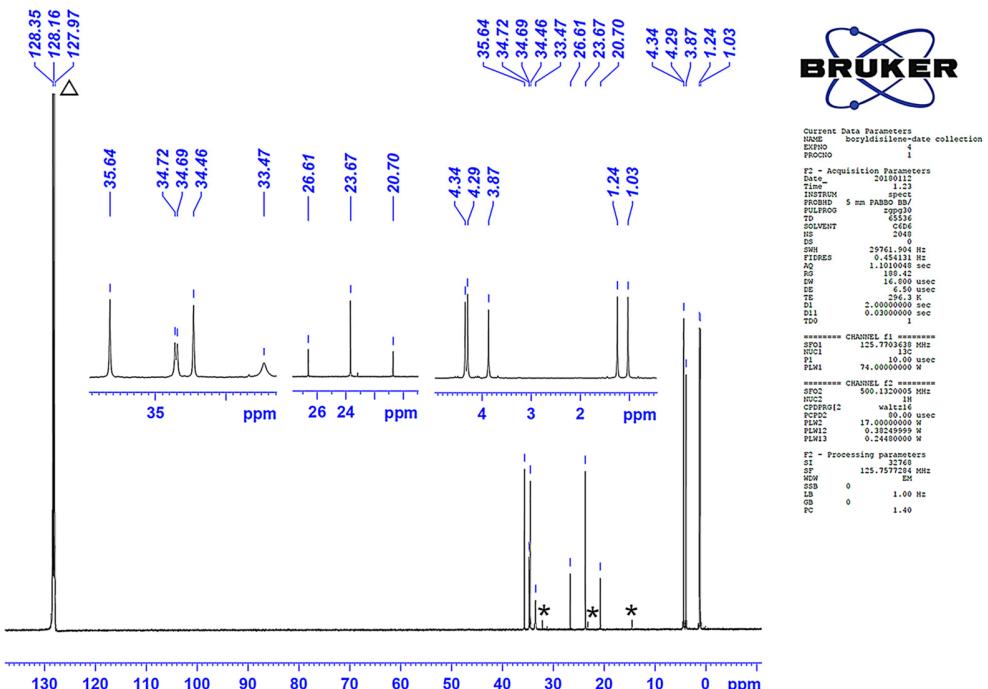


Figure S2. $^{13}\text{C}\{^1\text{H}\}$ NMR spectrum of **3** in C_6D_6 at 296 K ($\triangle = \text{C}_6\text{D}_6$, * = hexane).

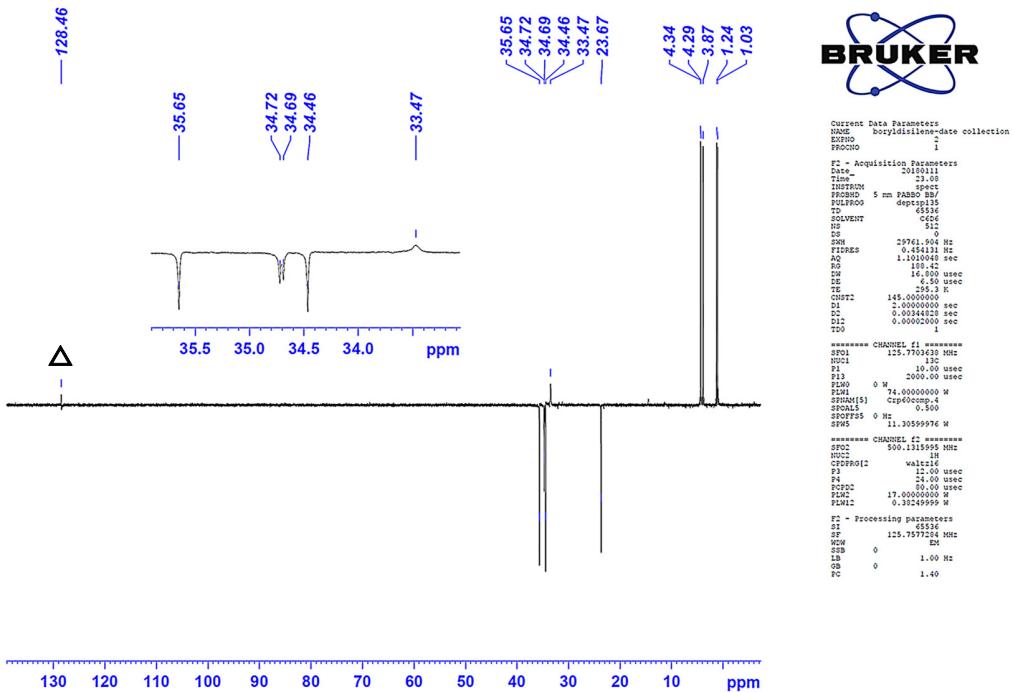


Figure S3. $^{13}\text{C}\{^1\text{H}\}$ NMR spectrum of **3** using DEPT 135 pulse sequence in C_6D_6 at 295 K.

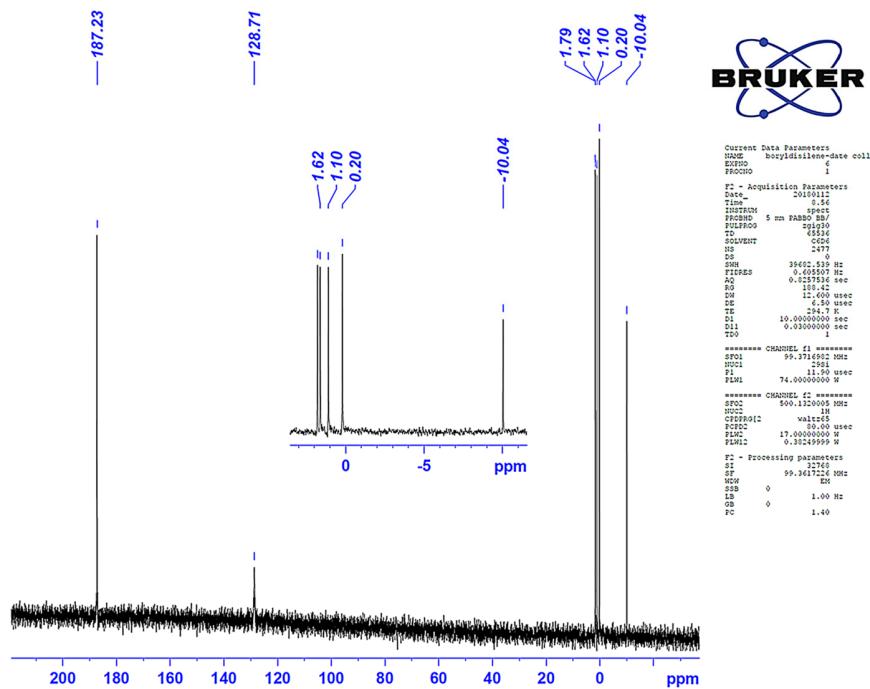


Figure S4. $^{29}\text{Si}\{^1\text{H}\}$ NMR spectrum of **3** using the inverse-gated pulse sequence in C_6D_6 at 295 K.

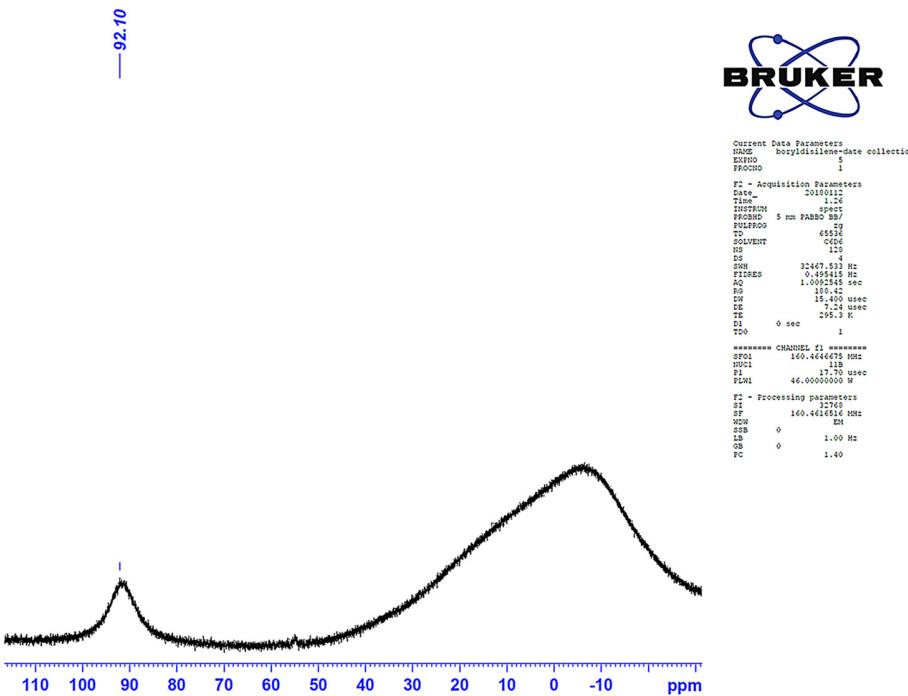


Figure S5. ^{11}B NMR spectrum of **3** in C_6D_6 at 295 K.

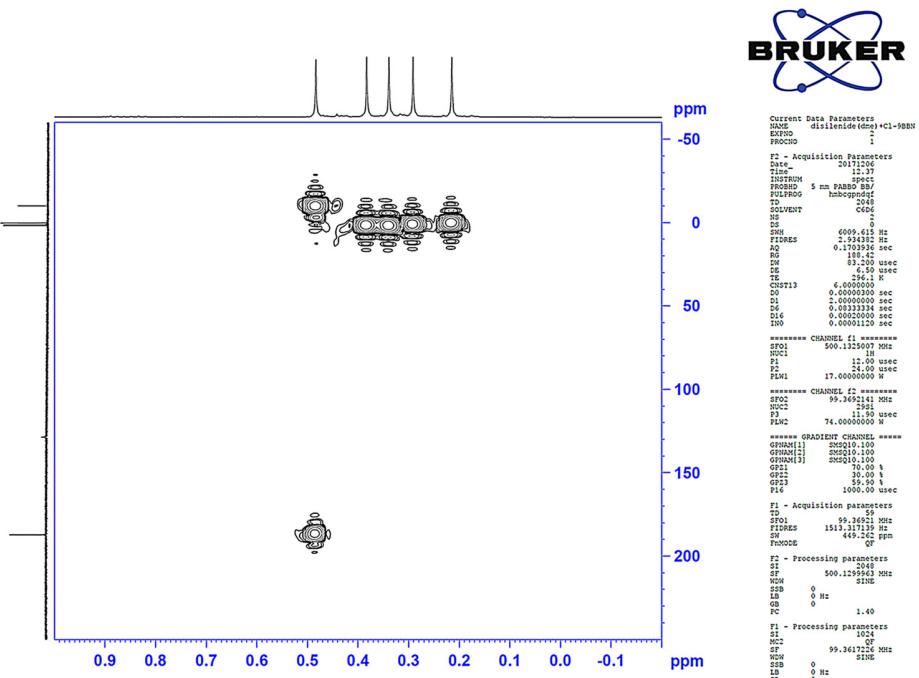


Figure S6. $^{29}\text{Si}-^1\text{H}$ 2D HMBC NMR spectrum of **3** in C_6D_6 at 296 K.

Diboryldisilene 4

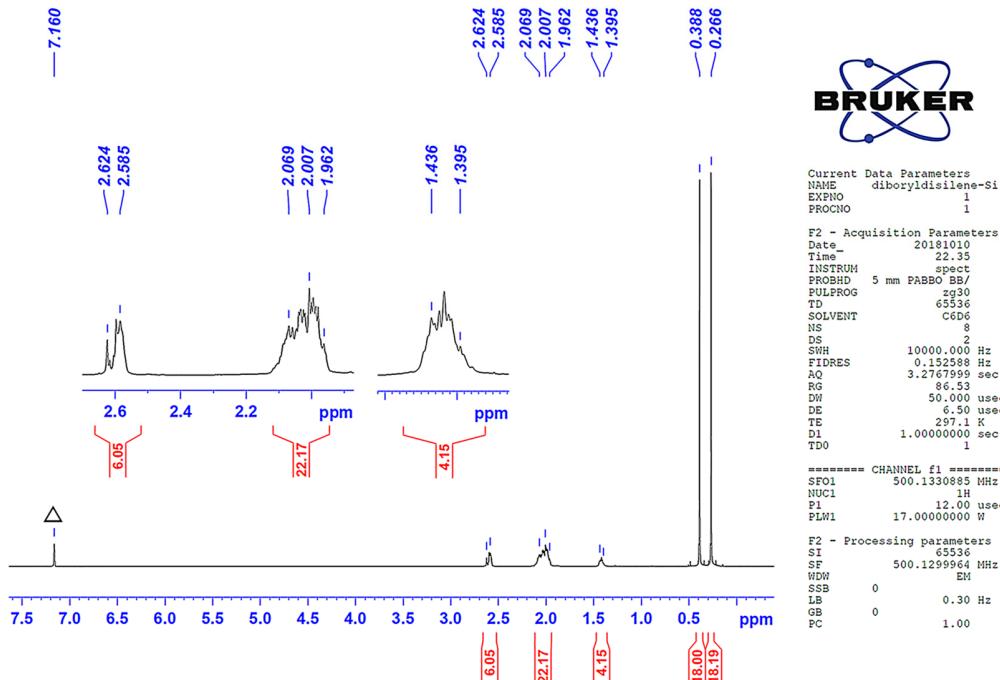


Figure S7. ^1H NMR spectrum of 4 in C_6D_6 at 297 K ($\triangle = \text{C}_6\text{D}_5\text{H}$).

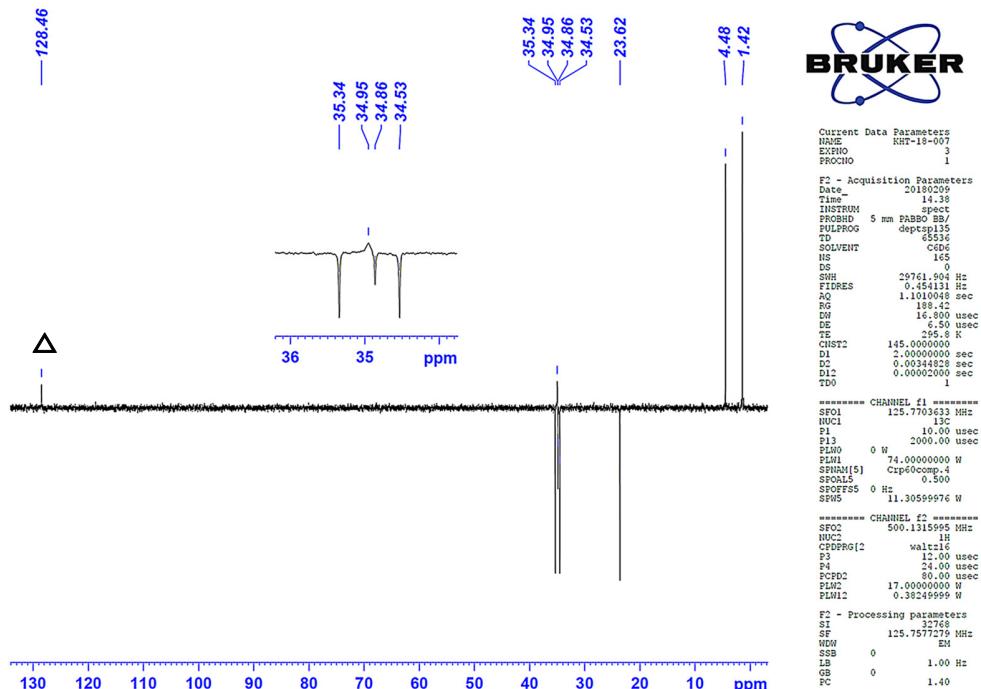


Figure S8. $^{13}\text{C}\{^1\text{H}\}$ NMR spectrum of 4 using DEPT 135 pulse sequence in C_6D_6 at 296 K ($\triangle = \text{C}_6\text{D}_5\text{H}$).

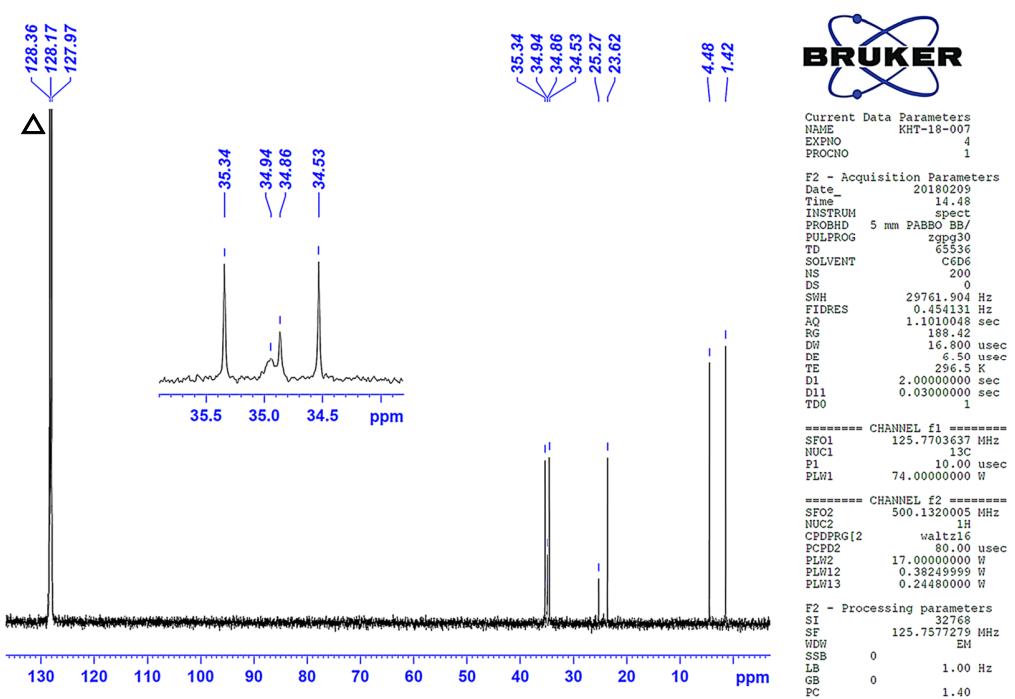


Figure S9. $^{13}\text{C}\{\text{H}\}$ NMR spectrum of **4** in C_6D_6 at 297 K ($\triangle = \text{C}_6\text{D}_6$).

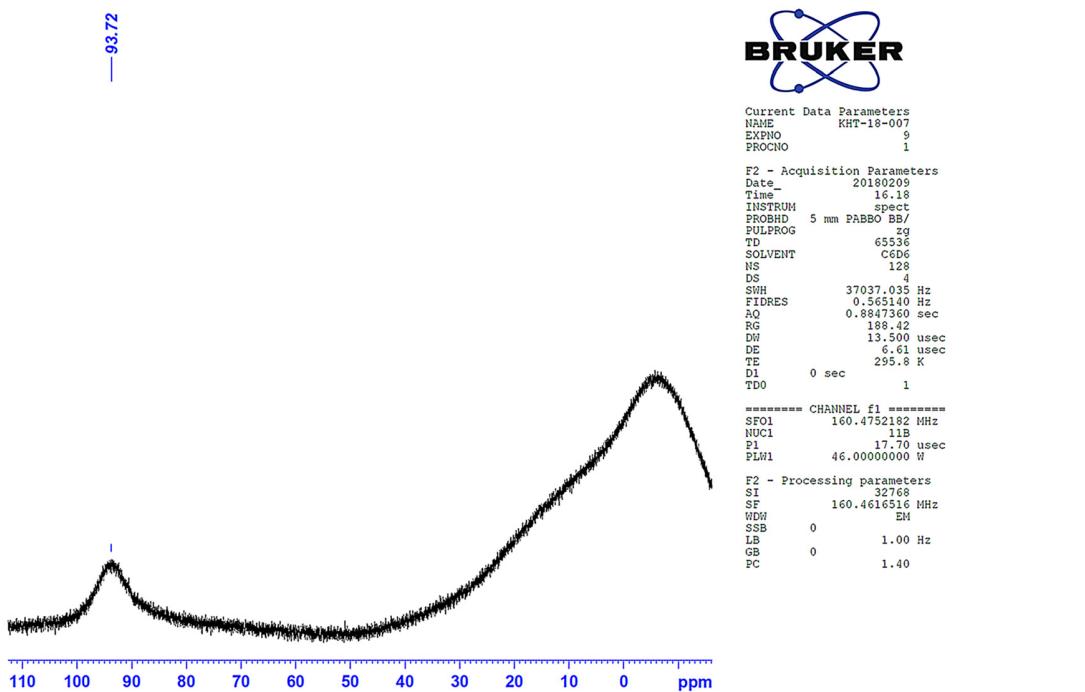


Figure S10. ^{11}B NMR spectrum of **4** in C_6D_6 at 296 K.

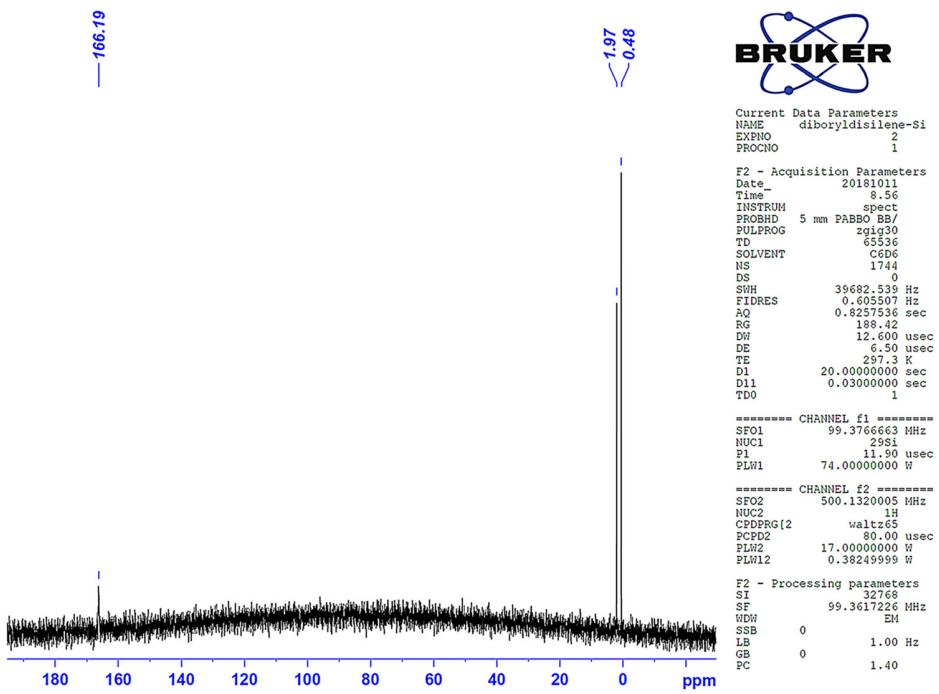


Figure S11. $^{29}\text{Si}\{^1\text{H}\}$ NMR spectrum of **4** using the inverse-gated pulse sequence in C_6D_6 at 297 K.

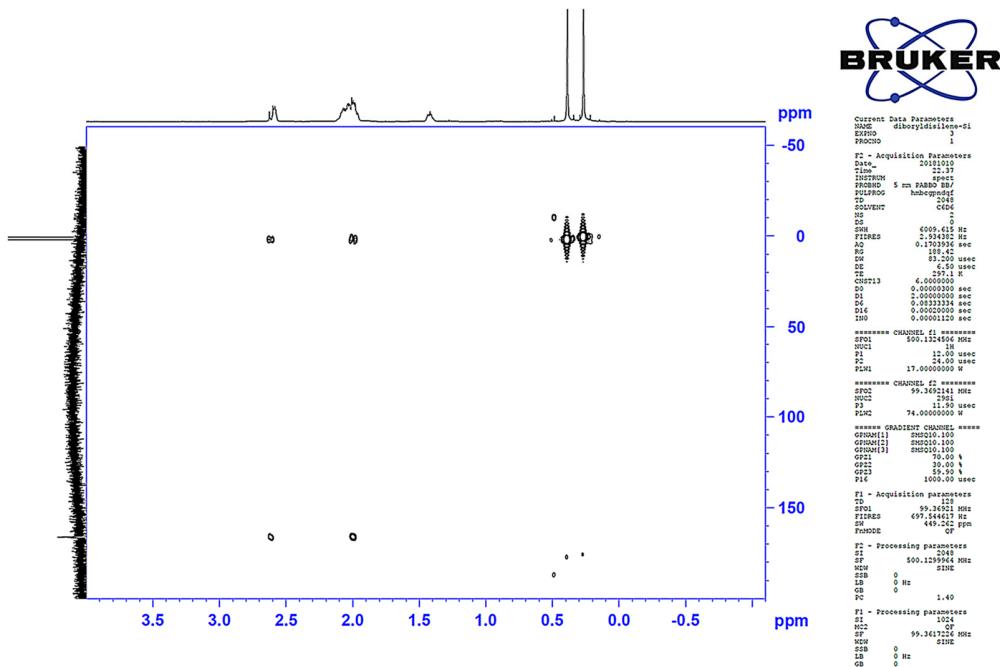


Figure S12. $^{29}\text{Si}-^1\text{H}$ 2D HMBC NMR spectrum of **4** in C_6D_6 at 297 K.

DMAP-coordinated Boryldisilene 5

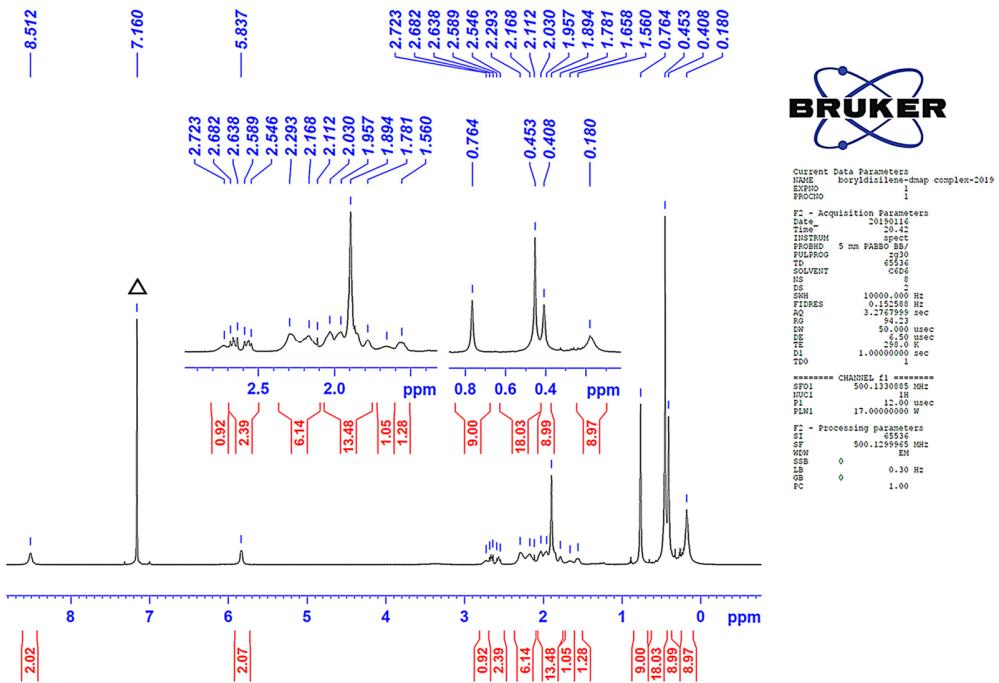


Figure S13. ^1H NMR spectrum of **5** in C_6D_6 at 298 K ($\triangle = \text{C}_6\text{D}_5\text{H}$).

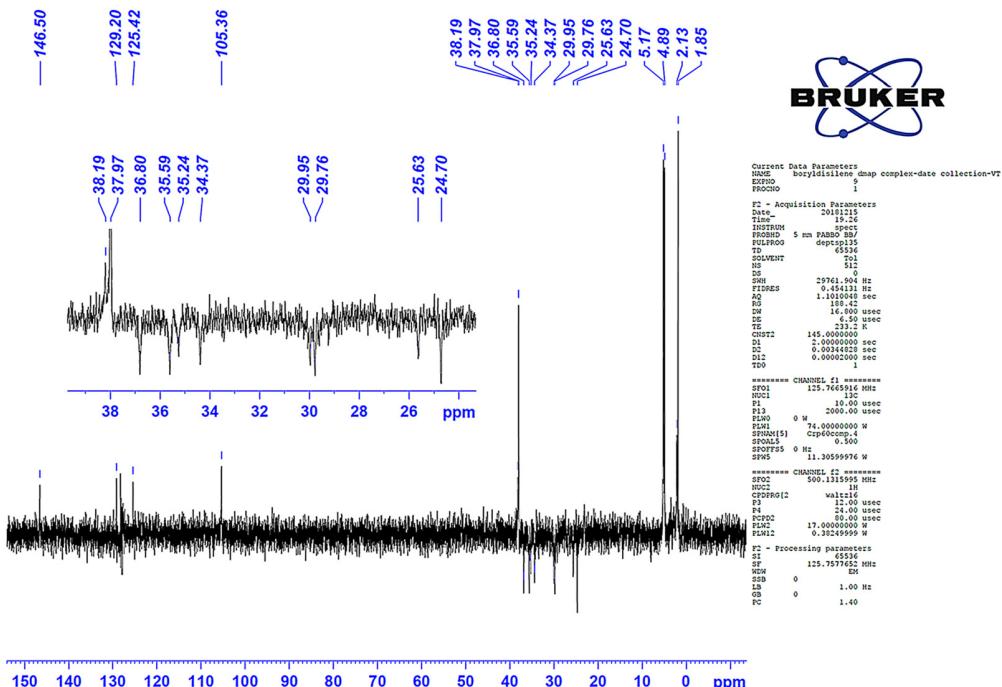


Figure S14. $^{13}\text{C}\{^1\text{H}\}$ NMR spectrum of **5** using DEPT 135 pulse sequence in toluene- d_8 at -40°C.

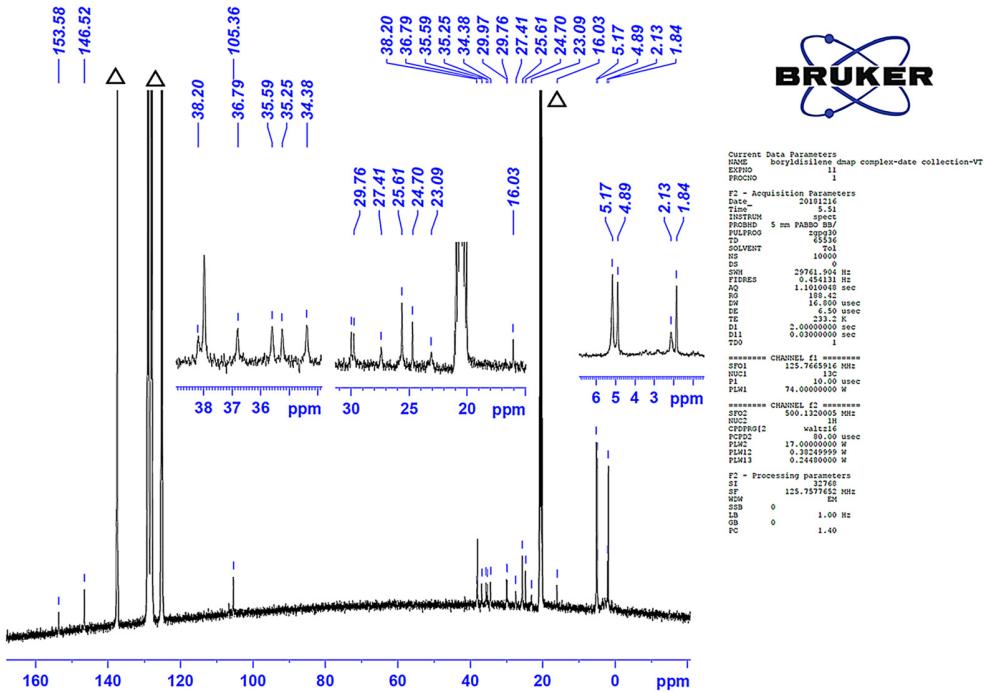


Figure S15. $^{13}\text{C}\{\text{H}\}$ NMR spectrum of **5** in toluene-*d*₈ at -40°C (\triangle = toluene-*d*₈).

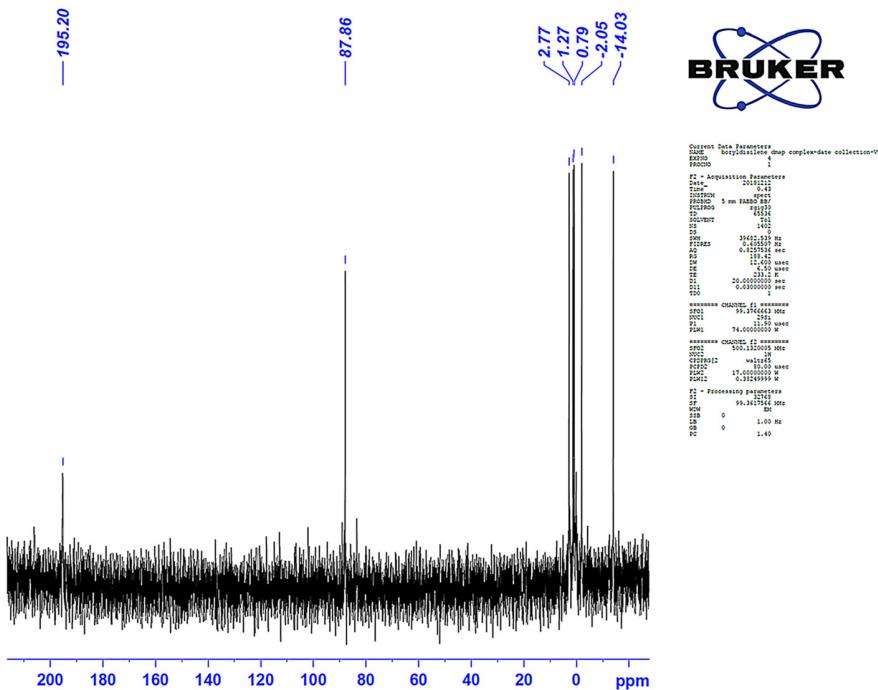


Figure S16. $^{29}\text{Si}\{\text{H}\}$ NMR spectrum of **5** in toluene-*d*₈ at -40 °C.

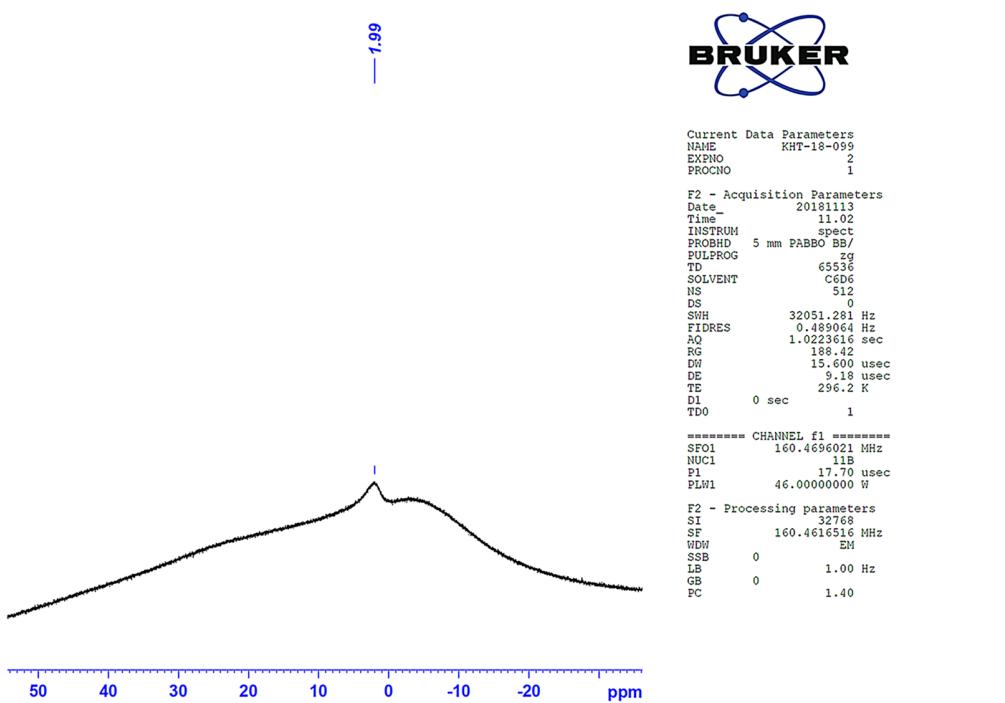


Figure S17. ^{11}B NMR spectrum of **5** in C_6D_6 at 296 K.

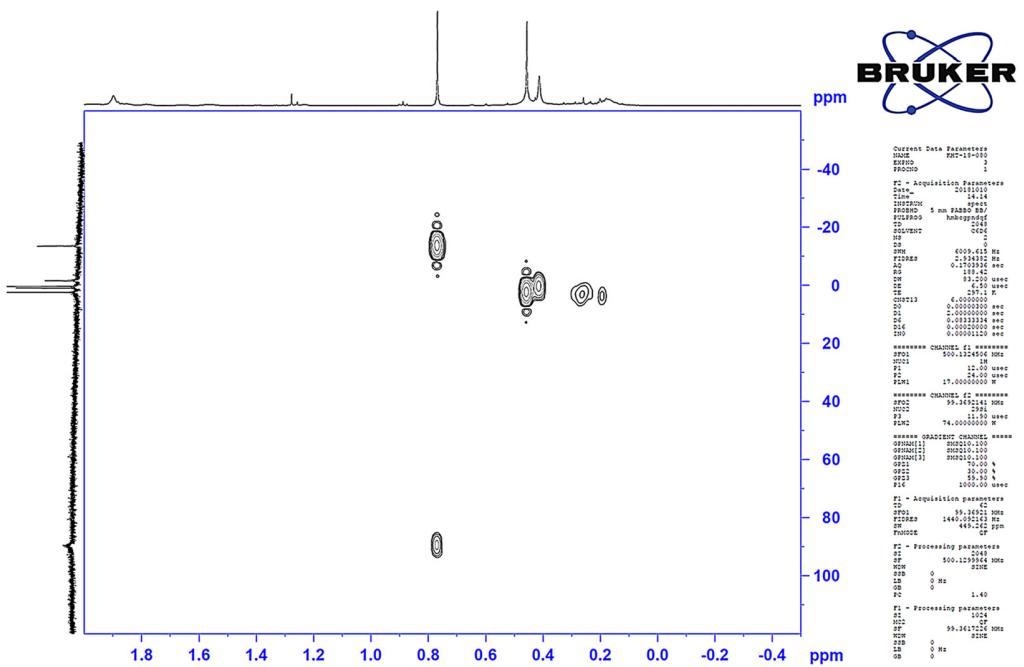


Figure S18. ^{29}Si - ^1H 2D HMBC NMR spectrum of **5** in C_6D_6 at 297 K.

Reaction of 5 and BPh₃

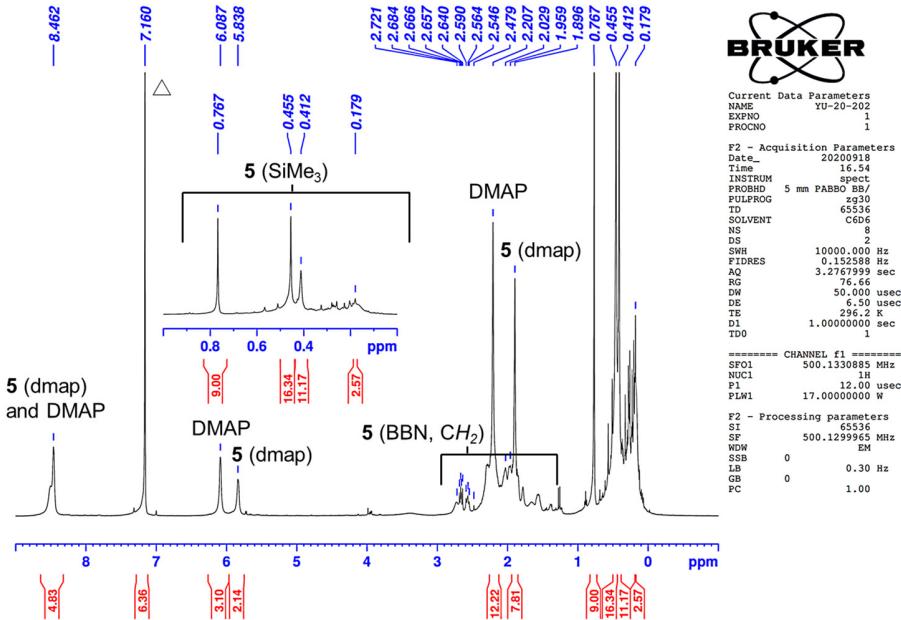


Figure S19. ¹H NMR spectrum of DMAP adduct 5 in C₆D₆ at 296 K ($\triangle = \text{C}_6\text{D}_5\text{H}$).

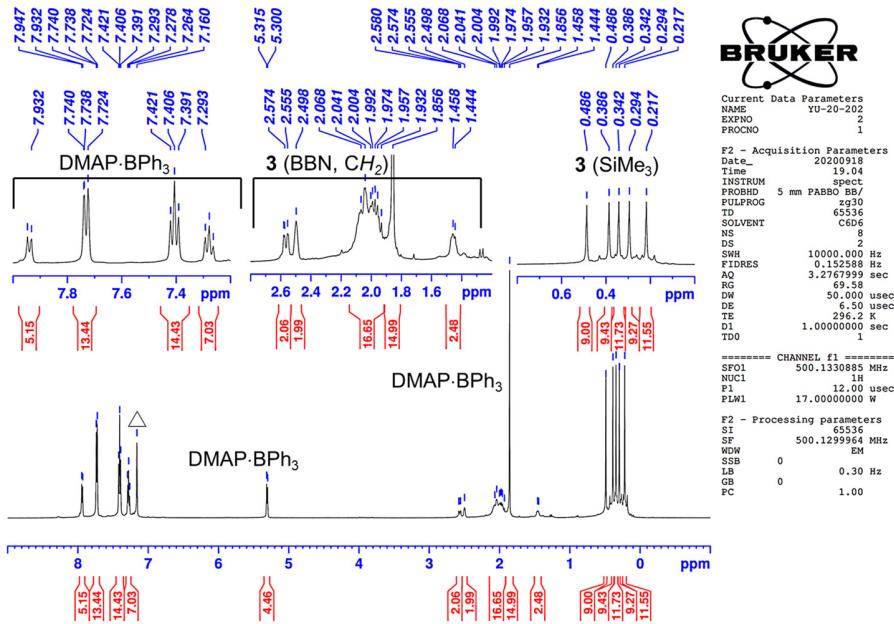


Figure S20. ¹H NMR spectrum of the reaction mixture after addition of B(C₆H₅)₃ in C₆D₆ at 296 K ($\triangle = \text{C}_6\text{D}_5\text{H}$).

Reaction of 5 and Me₃SiCl

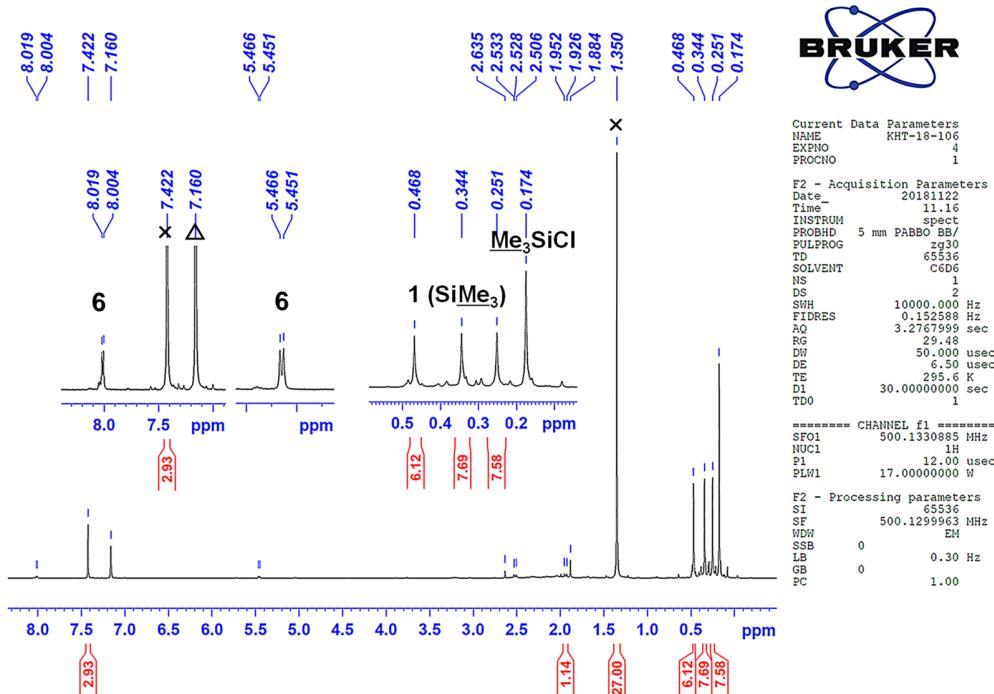


Figure S21. ¹H NMR spectrum of reaction mixture of **5** and Me₃SiCl in C₆D₆ at 296 K (\triangle =C₆D₅H, \times =Mes*H).

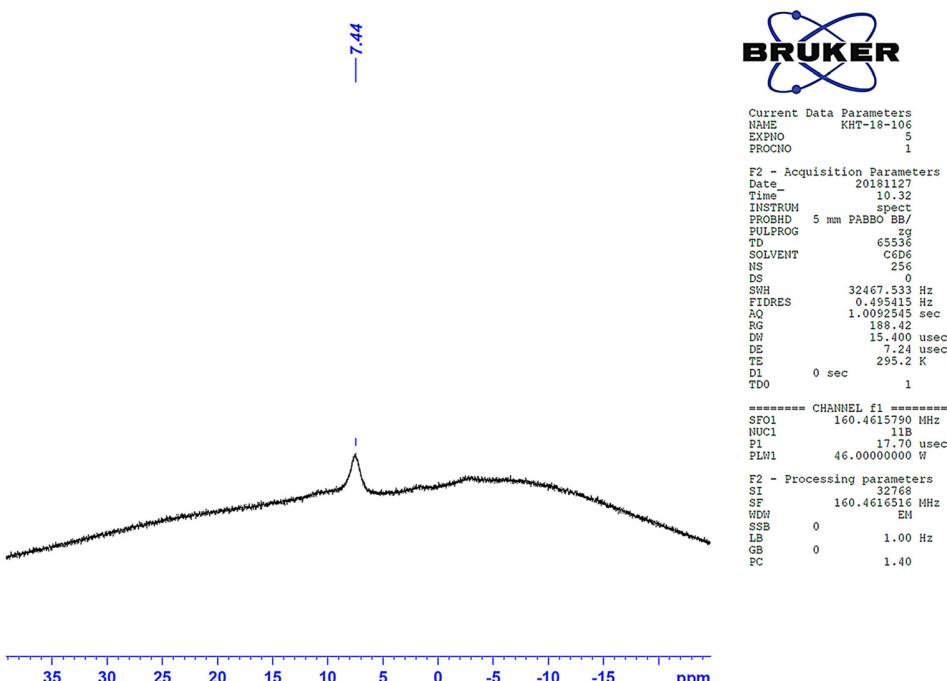


Figure S22. ¹¹B NMR spectrum of reaction mixture of **5** and Me₃SiCl at 295 K.

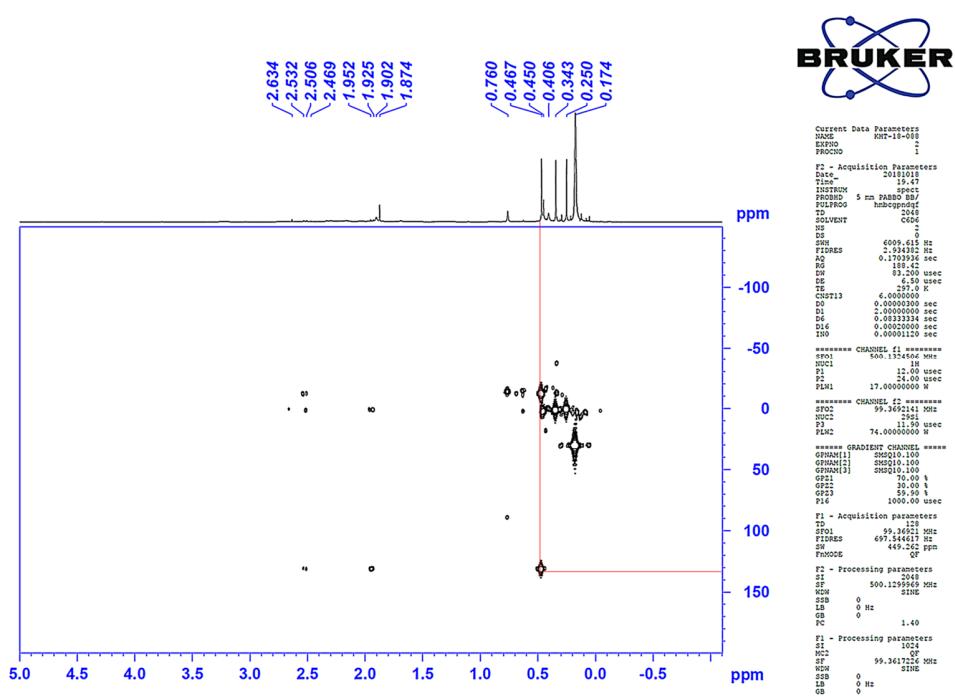


Figure S23. ^{29}Si - ^1H 2D HMBC NMR spectrum of reaction mixture of **5** and Me_3SiCl in C_6D_6 at 297 K.

Reaction of 4 and DMAP Followed by Me₃SiCl

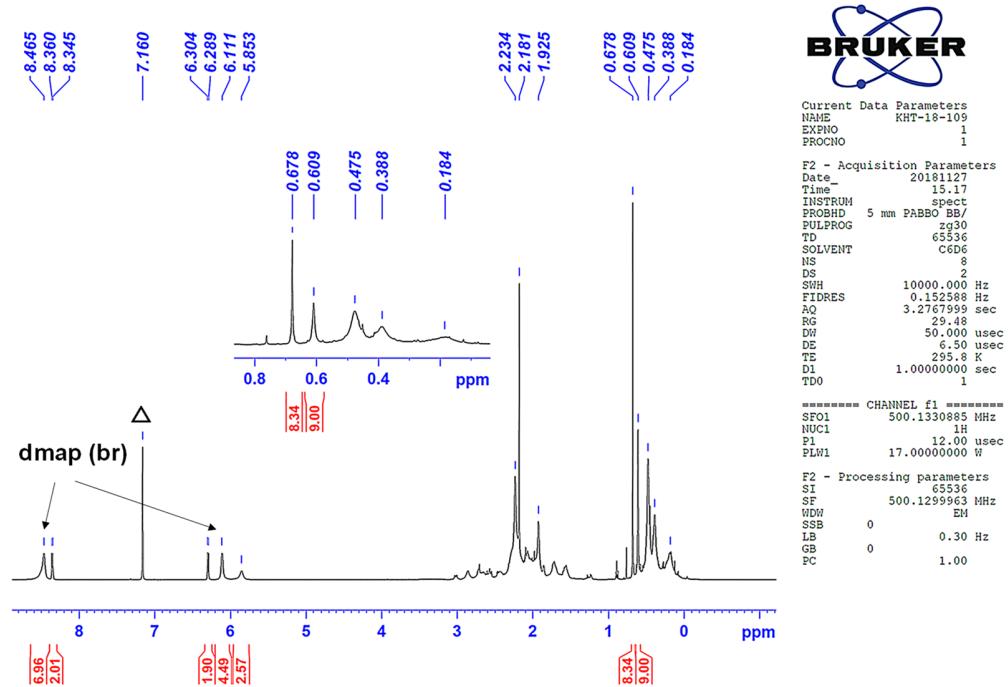


Figure S24. ¹H NMR spectrum of the reaction mixture of **4** and DMAP (2 equiv) in C₆D₆ recorded at 296 K (\triangle =C₆D₅H).

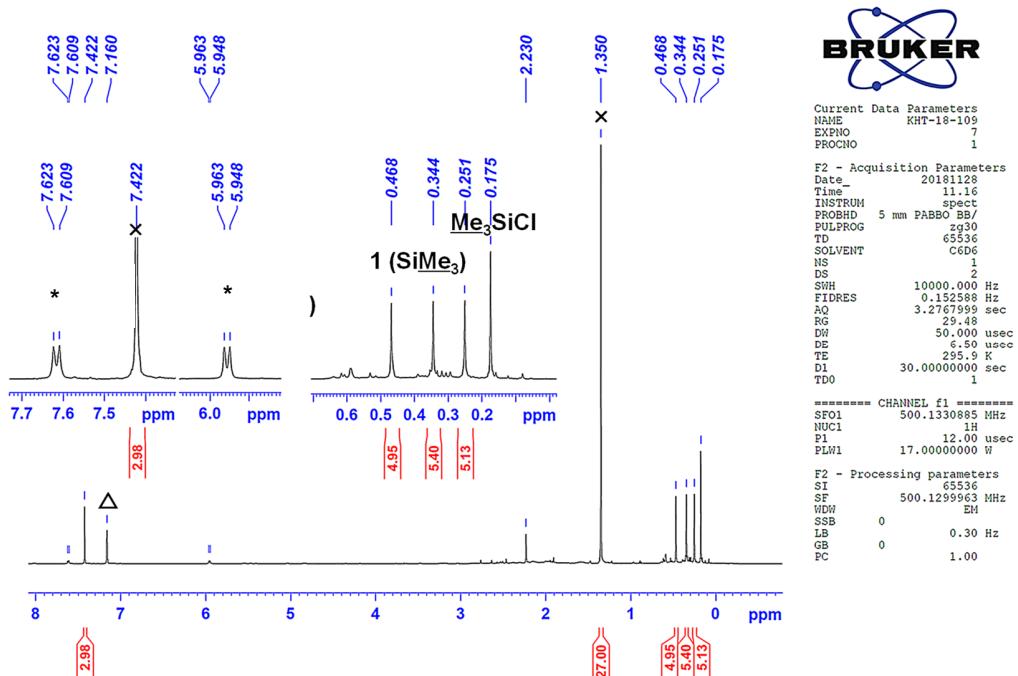


Figure S25. ¹H NMR spectrum of the reaction mixture of **4**, DMAP and Me₃SiCl after heating 60 °C in C₆D₆ recorded at 296 K (\triangle =C₆D₅H, \times =Mes*H, * = unidentified byproduct).

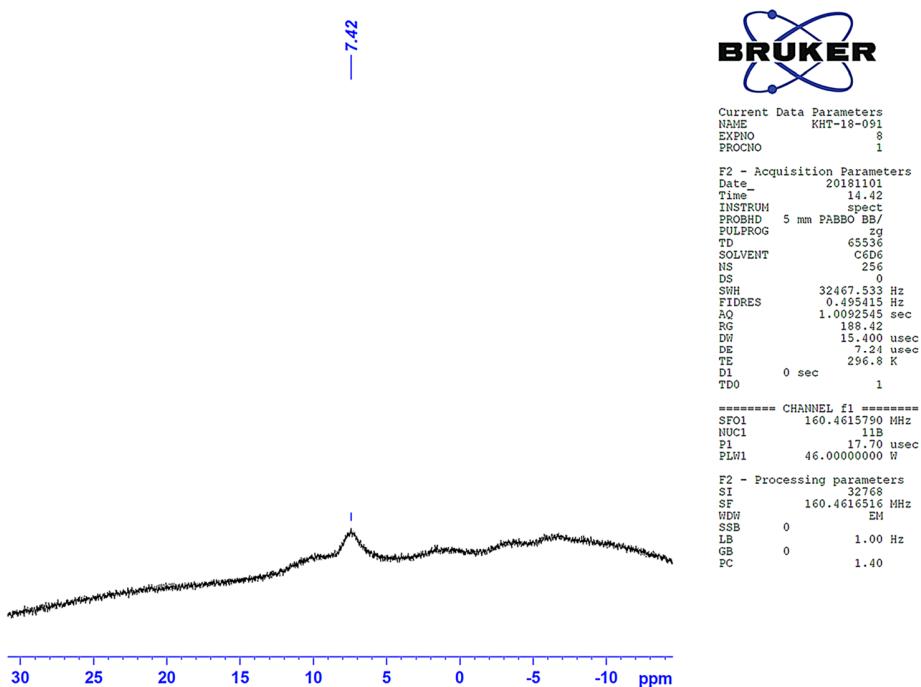


Figure S26. ^{11}B NMR spectrum of reaction mixture of **4**, DMAP and Me_3SiCl after heating $60\text{ }^\circ\text{C}$ in C_6D_6 recorded at 297 K .

Reaction of DMAP and BBNCl

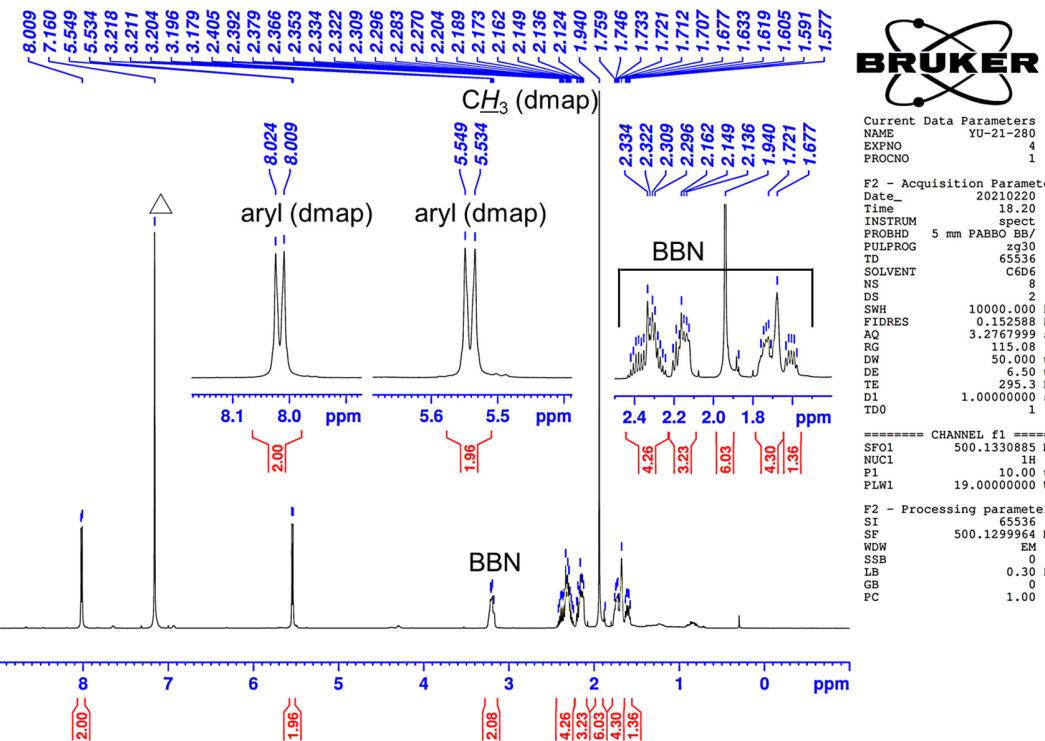


Figure S27. ^1H NMR spectrum of **6** in C_6D_6 at 295 K ($\triangle = \text{C}_6\text{D}_5\text{H}$).

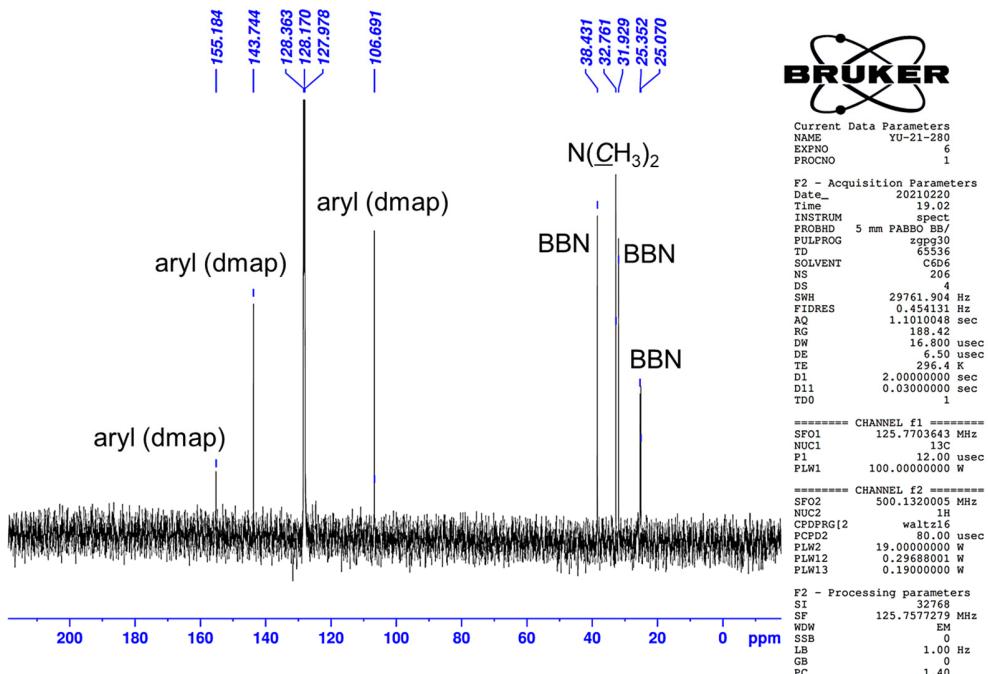


Figure S28. $^{13}\text{C}\{^1\text{H}\}$ NMR spectrum of **6** in C_6D_6 at 296 K.

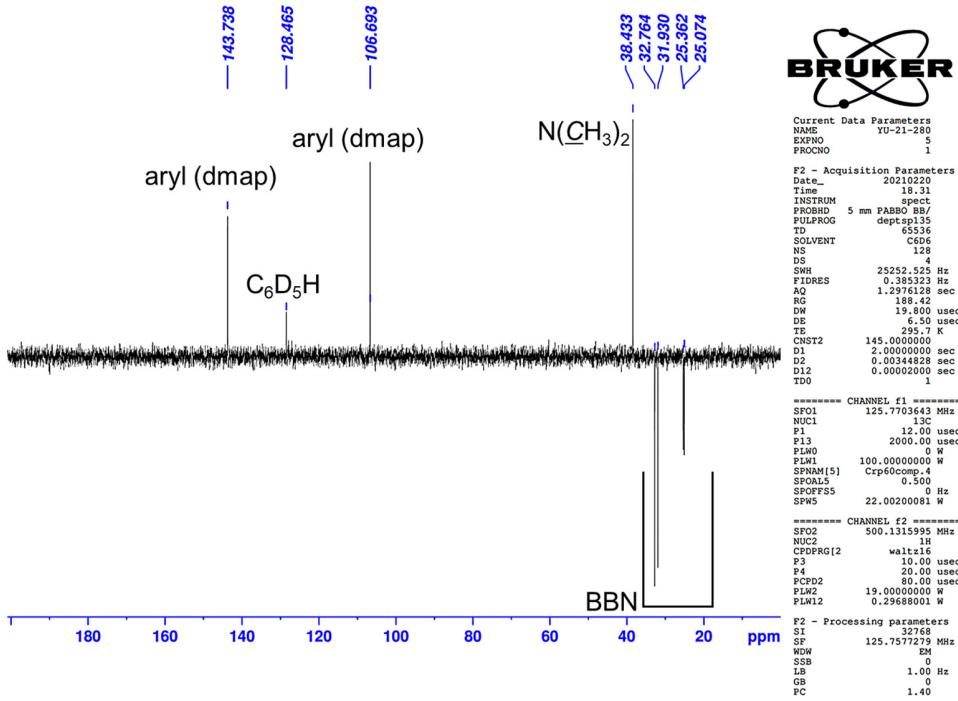


Figure S29. $^{13}\text{C}\{^1\text{H}\}$ NMR spectrum of **6** using DEPT 135 pulse sequence in C_6D_6 at 296 K.

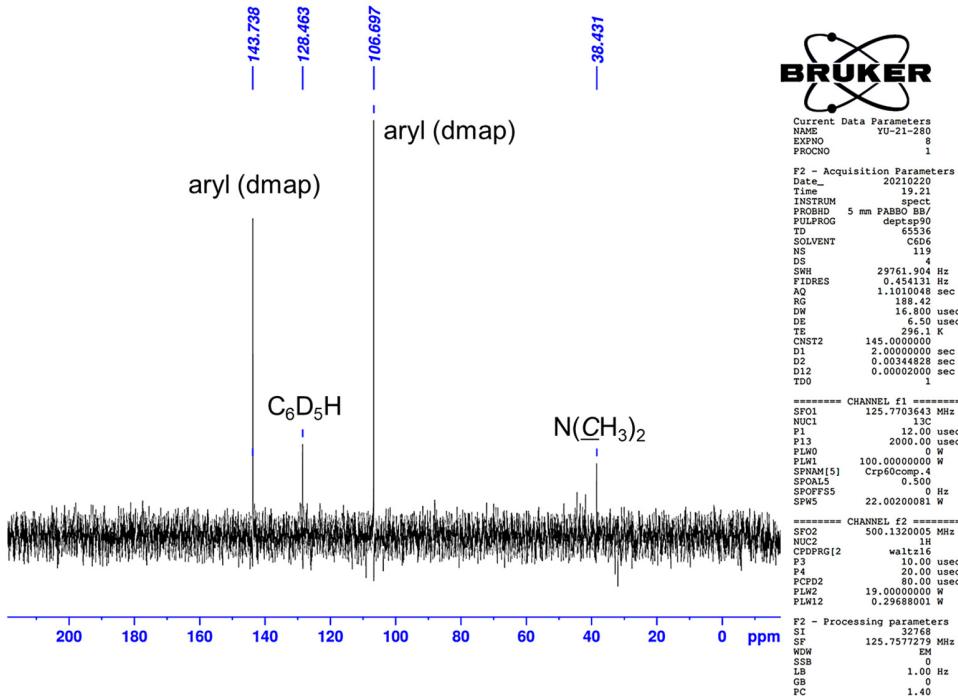


Figure S30. $^{13}\text{C}\{^1\text{H}\}$ NMR spectrum of **6** using DEPT 90 pulse sequence in C_6D_6 at 296 K.

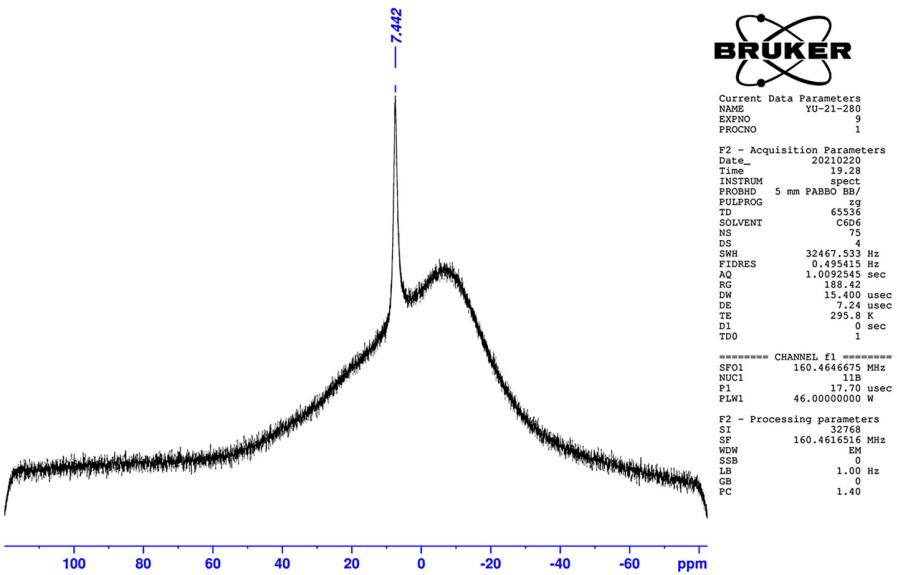


Figure S31. ^{11}B NMR spectrum of **6** in C_6D_6 at 296 K.

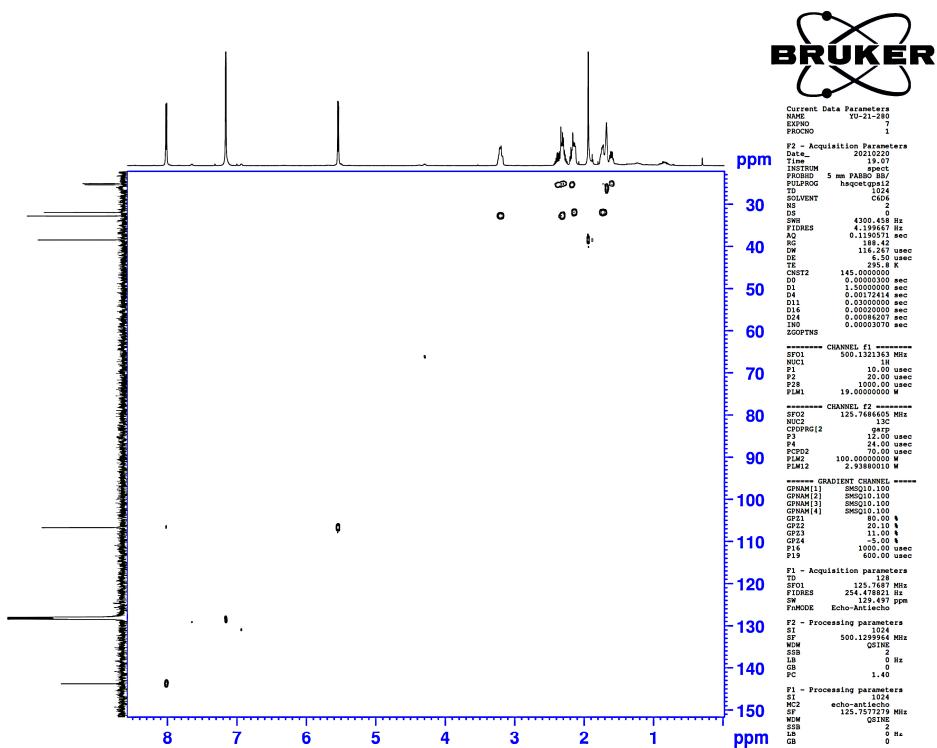


Figure S32. $^{13}\text{C}-^1\text{H}$ 2D HSQC NMR spectrum of **6** in C_6D_6 at 296 K.

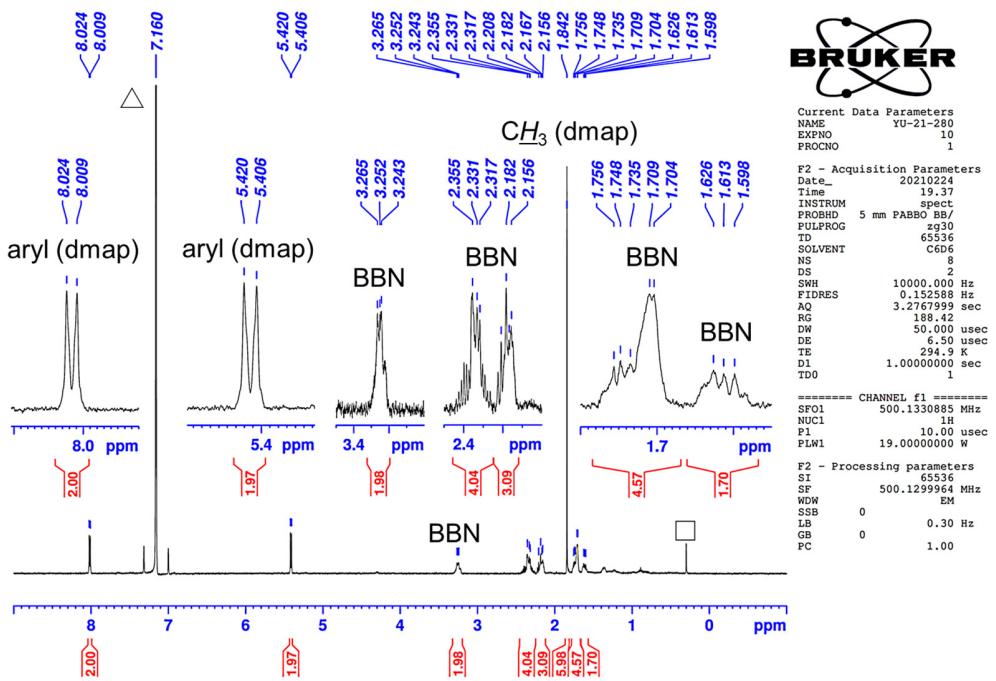


Figure S33. ^1H NMR spectrum of **6** in C_6D_6 at 295 K (low concentration, $\triangle = \text{C}_6\text{D}_5\text{H}$, $\square =$ silicon grease).

2. Details of Theoretical Study

Optimized Structures of 3, 4, and 5

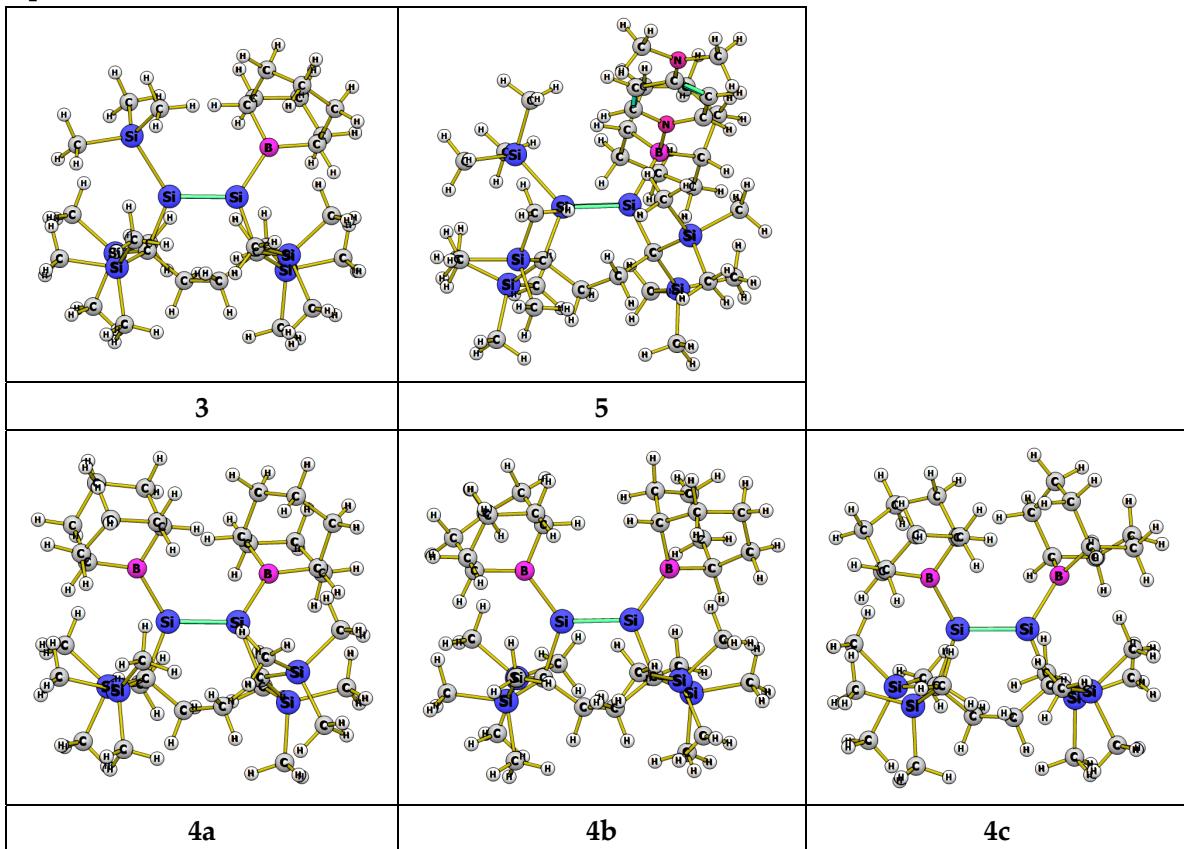


Figure S34. Optimized structures of 3, three conformers of 4 and 5.

Table S1. Selected Structural Parameters and Energy Levels of Frontier Orbitals of 3 and 5 Optimized at the B3PW91-D3/6-31(d) Level of Theory

Compound	distance/Å			angle sum/°		twist angle/°		Energy ^a /eV		$\lambda_{\max}^{\text{a}}/\text{nm}$	JOB
	Si=Si	Si-B	B-N	=Si(-Si)	=Si(-B)	Si-Si	Si-B	HOMO	LUMO	(f) ^a	
3_{opt}	2.19225	1.97039	—	359.10	358.8	20.2	2.5	-4.79	-2.03	487.86 (0.3132)	ti522SiB_2
3 (solid)	2.1990(8)	1.994(3)	—	359.16(6)	359.15(8)	10.0	5.0	—	—	—	XRD
3 (solution)	—	—	—	—	—	—	—	—	—	490 ($\epsilon 1.9 \times 10^4$)	in hexane
5_{opt}	2.19009	2.10907	1.62786	359.69	359.14	8.1	—	-4.06	-0.63 (LUMO+2, π^*)	(0.2108) ($\pi \rightarrow \pi^*$)	ti522SiBDMAP

a) Excitation energy and oscillator strength were calculated at the B3LYP/6-311(2df)[Si], 6-311G(d)[C, B, H] level of theory (solvent = hexane).

Table S2. Selected Structural Parameters and Energy Levels of Frontier Orbitals of **4** Optimized at the B3PW91-D3/6-31(d) Level of Theory

Compound	distance/Å		twist angle			Energy ^a /eV		$\lambda_{\text{max},\text{a}}/\text{nm}$ (f) ^a	$\Delta G/(\text{kJ/mol})$	JOB
	Si=Si	Si–B	Si=Si	Si–B	Si–B	HOMO	LUMO			
4a_{opt}	2.20152	1.98758 1.99036	27.7	8.3	8.1	-4.90	-2.53	581.07 (0.2599)	0.0	ti552B2conf3
4b_{opt}	2.20285	1.98078 2.00371	18.9	13.2	42.6	-4.86	-2.29	539.35 (0.3119)	0.34	ti552B2conf1
4c_{opt}	2.19394	1.96273 2.03035	22.2	0.4	72.3	-4.70	-2.08	623.42 (0.0506)	11.68	ti552B2conf2
4 (solid)	2.2114(5)	1.9851(14) 2.0156(15)	17.7	15.5	41.2	-	-	-	-	XRD
4 (solution)	-	-	-	-	-	-	-	576 (ε 5260)	-	in hexane

a) Excitation energy and oscillator strength were calculated at the B3LYP/6-311(2df)[Si], 6-311G(d)[C, B, H] level of theory (solvent = hexane).

If the ratio of the molecular number of conformers 2 relative to conformer 1 (N_2/N_1) obeys the Boltzmann distribution, N_2/N_1 should be

$$\frac{N_2}{N_1} = e^{-\frac{E_2 - E_1}{kT}} = e^{-\frac{340 \text{ J/mol} + 6.02 \times 10^{23} \text{ mol}^{-1}}{1.381 \times 10^{-23} \text{ J K}^{-1} \times 298.15 \text{ K}}} = e^{-0.137} = 0.872$$

, where Boltzmann constant $k = 1.381 \times 10^{-23} \text{ J K}^{-1}$, Avogadro constant = $6.02 \times 10^{23} \text{ mol}^{-1}$, and temperature $T = 298.15 \text{ K}$. This value suggests that both conformers 1 (**4a**) and 2 (**4b**) can be observed.

Natural Bond Orbital (NBO) Analysis

Table S3. NBO Analysis

Compound (R1, R2)	NPA charge				bond order (WBI) [distance/Å]		second order perturbation analysis donor NBO → acceptor NBO, stabilization energy in kcal/mol
	Si1	Si2	B1	B2	Si=Si	Si–B	
1 (SiMe ₃ , SiMe ₃)	0.32	0.32	-	-	1.7972 [2.17640]	-	-
3 (BBN, SiMe ₃) [JOB:ti552B2conf1_NBO2]	0.43	0.60	0.30	-	1.6581 [2.19225]	1.1127 [1.97039]	BD2(Si1–Si2)→LV(B2), 25.62
4 (BBN, BBN) conformer 1 [JOB:ti552B2conf3_NBO2]	0.69	0.67	0.33	0.35	1.5826 [2.20152]	1.0647 [1.98758]	BD2(Si1–Si2)→LV(B1), 22.01 BD2(Si1–Si2)→LV(B2), 22.03
4 (BBN, BBN) conformer 2 [JOB:ti552B2conf1_NBO2]	0.64	0.68	0.33	0.38	1.6069 [2.20285]	1.0672 [1.99036]	BD2(Si1–Si2)→LV(B1), 22.83 BD2(Si1–Si2)→LV(B2), 15.52
4 (BBN, BBN) conformer 3 [JOB:ti552B2conf2_NBO2]	0.56	0.72	0.28	0.45	1.6121 [2.19394]	1.0419 [2.00371]	BD2(Si1–Si2)→LV(B1), 28.56 BD2(Si1–Si2)→LV(B2), 0.91
12 (BBN·DMAP, SiMe ₃)	0.74	0.19	0.17	-	1.7721 [2.19009]	0.9060 [2.10907]	-

GIAO Calculations

Table S4. ^{29}Si NMR Chemical Shifts Calculated at the B97-D3/def2-TZVP Level of Theory

Compound (R1, R2)	Calculated Chemical Shift Relative to TMS (absolute chemical shift)		Observed Chemical Shift Relative to TMS	
	Si-R1	Si-R2	Si-R1	Si-R2
1 (SiMe ₃ , SiMe ₃) [JOB:ti5552Si2_NMR15]	141.4756 (184.4999)	141.9943 (183.9812)	131.4	131.4
3 (BBN, SiMe ₃) [JOB:ti5552SiB_2_NMR15]	136.2112 (189.7643)	209.0724 (116.9031)	128.7	187.2
4 (BBN, BBN) conformer 1 [JOB:ti5552B2conf3_NMR15]	201.0537 (124.9218)	195.3660 (130.6095)	166.2	166.2
4 (BBN, BBN) conformer 2 [JOB:ti5552B2conf1_NMR15]	147.2043 (178.7712)	184.2626 (141.7129)	166.2	166.2
4 (BBN, BBN) conformer 3 [JOB:ti5552B2conf2_NMR15]	107.5750 (218.4005)	220.2537 (105.7218)	166.2	166.2
5 (BBN·DMAP, SiMe ₃) [JOB:ti5552SiBDMAP_NMR15]	237.6736 (88.3019)	73.0990 (252.8765)	195.2	87.9
Me ₄ Si	0 (325.9755)	0 (325.9755)	0	0

TD-DFT Calculations

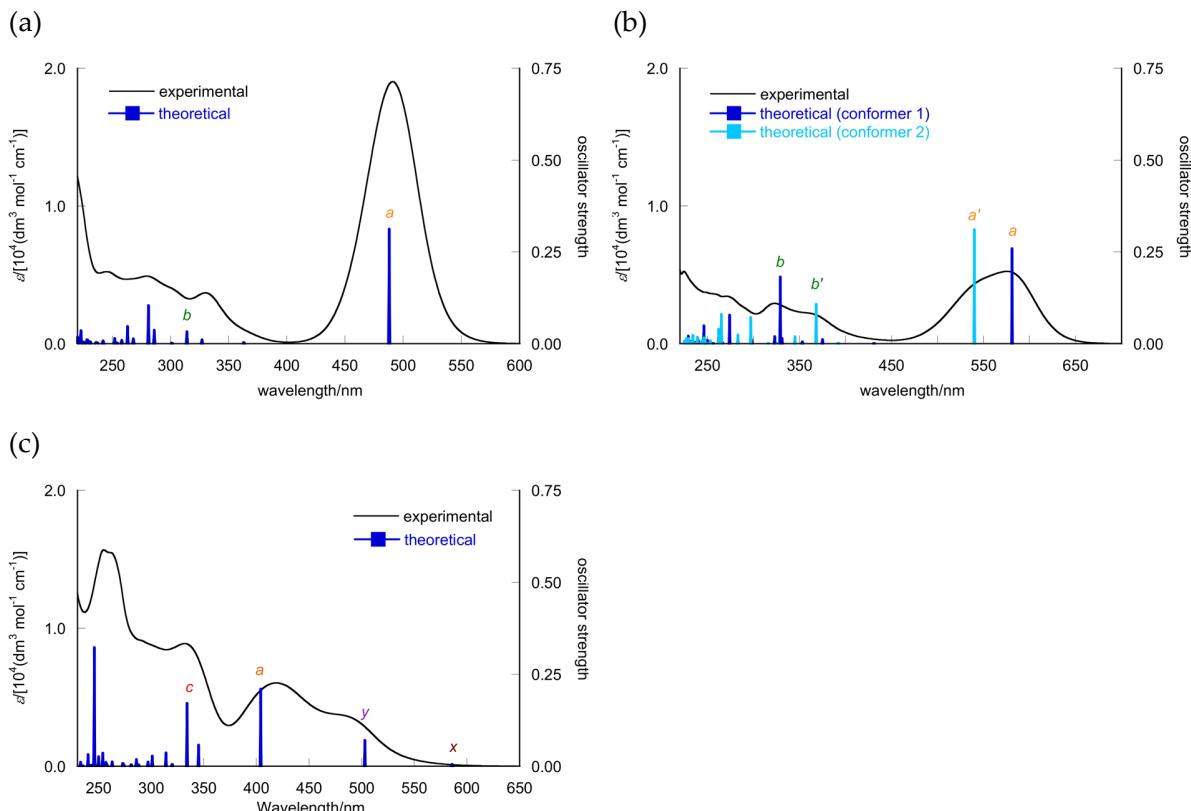


Figure S35. UV-vis absorption spectra of (a) **3**, (b) **4**, and (c) **5** in hexane at room temperature as well as band positions and oscillator strengths (vertical bars) calculated at the B3LYP-D3/B1//B3PW91-D3/6-31G(d) level of theory (B1: 6-311+G(2df) [Si], 6-311G(d) [others]).

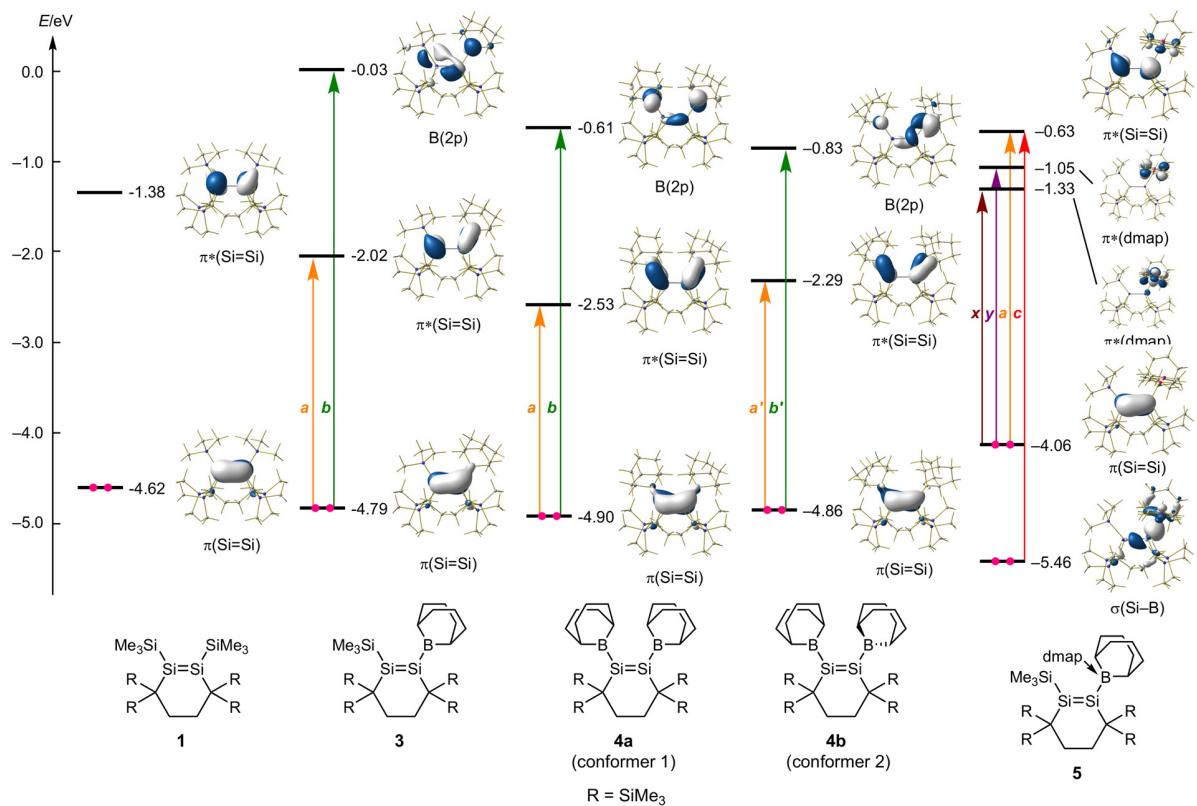


Figure S36. Selected frontier orbitals of **1**_{opt}, **3**_{opt}, **4a**_{opt}, **4b**_{opt}, and **5**_{opt} at the B3LYP-D3/B1//B3PW91-D3/6-31G(d) level of theory (B1: 6-311+G(2df) [Si], 6-311G(d) [others]).

Table S5. Transition Energy, Wavelength, and Oscillator Strengths of the Electronic Transition of **3** Calculated at the TD-B3LYP-D3/B1 [hexane] Level of Theory (The 151st orbital is Highest Occupied $\pi(\text{Si}=\text{Si})$ Orbital Shown in Figure S36.)

Excited State	1:	Singlet-A	2.9872 eV	415.04 nm	f=0.2877	<S**2>=0.000
151 ->152		0.69518				
151 ->153		0.11330				
Excited State	2:	Singlet-A	3.5992 eV	344.48 nm	f=0.0313	<S**2>=0.000
151 ->152		-0.11190				
151 ->153		0.69246				
Excited State	3:	Singlet-A	4.1258 eV	300.51 nm	f=0.0030	<S**2>=0.000
150 ->152		0.69312				
151 ->155		0.10065				
Excited State	4:	Singlet-A	4.3196 eV	287.03 nm	f=0.0002	<S**2>=0.000
151 ->155		0.68555				
151 ->159		0.11591				
Excited State	5:	Singlet-A	4.4761 eV	276.99 nm	f=0.0424	<S**2>=0.000
149 ->152		0.19749				
151 ->154		0.66533				
151 ->156		0.10291				
Excited State	6:	Singlet-A	4.5836 eV	270.50 nm	f=0.0111	<S**2>=0.000
149 ->152		0.62840				
151 ->154		-0.22112				
151 ->156		0.20837				
Excited State	7:	Singlet-A	4.7063 eV	263.44 nm	f=0.0194	<S**2>=0.000
149 ->152		-0.24322				
151 ->156		0.64220				
151 ->161		0.10210				
Excited State	8:	Singlet-A	4.7498 eV	261.03 nm	f=0.0028	<S**2>=0.000
151 ->157		0.64418				
151 ->159		0.24822				
Excited State	9:	Singlet-A	5.0169 eV	247.13 nm	f=0.0144	<S**2>=0.000
147 ->152		0.18348				
148 ->152		0.56741				
151 ->158		0.35633				
Excited State	10:	Singlet-A	5.0728 eV	244.41 nm	f=0.0086	<S**2>=0.000

147 ->152	-0.16662	
148 ->152	-0.32729	
151 ->158	0.58163	
151 ->159	-0.11517	
Excited State 11:	Singlet-A	5.1184 eV 242.23 nm f=0.0002 <S**2>=0.000
151 ->157	-0.26149	
151 ->158	0.12306	
151 ->159	0.63119	
Excited State 12:	Singlet-A	5.1917 eV 238.81 nm f=0.0060 <S**2>=0.000
151 ->156	0.12630	
151 ->160	0.68687	
Excited State 13:	Singlet-A	5.2165 eV 237.68 nm f=0.0156 <S**2>=0.000
147 ->152	0.65314	
148 ->152	-0.24144	
Excited State 14:	Singlet-A	5.3088 eV 233.55 nm f=0.0096 <S**2>=0.000
151 ->156	-0.10846	
151 ->161	0.67346	
Excited State 15:	Singlet-A	5.3830 eV 230.33 nm f=0.0356 <S**2>=0.000
150 ->153	-0.26450	
151 ->162	0.60636	
151 ->163	-0.19038	
Excited State 16:	Singlet-A	5.4542 eV 227.32 nm f=0.0007 <S**2>=0.000
146 ->152	0.70095	
Excited State 17:	Singlet-A	5.5401 eV 223.79 nm f=0.0066 <S**2>=0.000
151 ->162	0.20779	
151 ->163	0.65667	
Excited State 18:	Singlet-A	5.6165 eV 220.75 nm f=0.0952 <S**2>=0.000
150 ->153	0.62037	
151 ->162	0.26315	
Excited State 19:	Singlet-A	5.7433 eV 215.88 nm f=0.0109 <S**2>=0.000
151 ->161	-0.18249	
151 ->164	0.66117	
151 ->167	0.18322	
Excited State 20:	Singlet-A	5.7879 eV 214.21 nm f=0.0088 <S**2>=0.000
151 ->165	0.67678	
151 ->169	0.11657	
Excited State 21:	Singlet-A	5.8762 eV 210.99 nm f=0.0010 <S**2>=0.000
143 ->152	-0.12193	
145 ->152	0.66444	
151 ->166	-0.18095	
Excited State 22:	Singlet-A	5.8940 eV 210.36 nm f=0.0001 <S**2>=0.000
145 ->152	0.18274	
151 ->166	0.64184	
151 ->169	0.15808	
Excited State 23:	Singlet-A	5.8957 eV 210.30 nm f=0.0028 <S**2>=0.000
144 ->152	-0.47087	
151 ->164	-0.12994	
151 ->167	0.47252	
Excited State 24:	Singlet-A	5.9048 eV 209.97 nm f=0.0108 <S**2>=0.000
144 ->152	0.45319	
151 ->164	-0.15663	
151 ->167	0.43649	
151 ->168	-0.19860	
151 ->171	0.10422	
Excited State 25:	Singlet-A	5.9386 eV 208.78 nm f=0.0033 <S**2>=0.000
144 ->152	0.22448	
151 ->167	0.11550	
151 ->168	0.61327	
151 ->171	-0.17674	
Excited State 26:	Singlet-A	5.9870 eV 207.09 nm f=0.0013 <S**2>=0.000
141 ->152	0.10158	
143 ->152	0.66884	
145 ->152	0.11864	
151 ->169	-0.14481	
Excited State 27:	Singlet-A	5.9994 eV 206.66 nm f=0.0059 <S**2>=0.000
143 ->152	0.14640	
151 ->165	-0.11510	
151 ->166	-0.16205	
151 ->169	0.63941	
Excited State 28:	Singlet-A	6.0027 eV 206.55 nm f=0.0645 <S**2>=0.000
140 ->152	0.11350	
142 ->152	-0.10613	
149 ->153	0.66477	
Excited State 29:	Singlet-A	6.0462 eV 205.06 nm f=0.0145 <S**2>=0.000
136 ->152	-0.17057	
139 ->152	0.19405	
140 ->152	0.45616	
142 ->152	-0.42530	
149 ->153	-0.15593	
Excited State 30:	Singlet-A	6.0632 eV 204.49 nm f=0.0071 <S**2>=0.000
151 ->168	0.21139	
151 ->171	0.63729	
Excited State 31:	Singlet-A	6.0800 eV 203.92 nm f=0.0129 <S**2>=0.000
151 ->170	0.59042	
151 ->172	0.32043	
Excited State 32:	Singlet-A	6.0993 eV 203.28 nm f=0.0013 <S**2>=0.000
136 ->152	-0.15082	
140 ->152	0.41682	
142 ->152	0.52167	
144 ->152	0.12136	

JOB: ti552SiB_2_TD2

Table S6. Transition Energy, Wavelength, and Oscillator Strengths of the Electronic Transition of **4a_{opt}** Calculated at the TD-B3LYP-D3/B1 [hexane] Level of Theory (The 177th orbital is

Highest Occupied π (Si=Si) Orbital Shown in Figure S36.)

```

Excited State 1: Singlet-A 2.1337 eV 581.07 nm f=0.2599 <S**2>=0.000
  177 -> 178  0.71146
  177 <- 178 -0.12290
This state for optimization and/or second-order correction.
Total Energy, E(TD-HF/TD-KS) = -3047.66254997
Copying the excited state density for this state as the 1-particle RhoCI density.
Excited State 2: Singlet-A 2.8777 eV 430.84 nm f=0.0017 <S**2>=0.000
  176 -> 178  0.70173
Excited State 3: Singlet-A 3.3071 eV 374.91 nm f=0.0124 <S**2>=0.000
  175 -> 178  0.70139
Excited State 4: Singlet-A 3.5151 eV 352.72 nm f=0.0059 <S**2>=0.000
  172 -> 178  0.10087
  174 -> 178  0.68892
Excited State 5: Singlet-A 3.7508 eV 330.56 nm f=0.0157 <S**2>=0.000
  172 -> 178  0.18565
  173 -> 178  0.63195
  177 -> 179 -0.22364
Excited State 6: Singlet-A 3.7644 eV 329.36 nm f=0.1827 <S**2>=0.000
  172 -> 178  0.13670
  173 -> 178  0.19586
  177 -> 179  0.65266
Excited State 7: Singlet-A 3.8423 eV 322.68 nm f=0.0204 <S**2>=0.000
  171 -> 178 -0.16809
  172 -> 178  0.63288
  173 -> 178 -0.20551
  174 -> 178 -0.10623
Excited State 8: Singlet-A 4.1620 eV 297.90 nm f=0.0111 <S**2>=0.000
  171 -> 178  0.68090
  172 -> 178  0.16133
Excited State 9: Singlet-A 4.3799 eV 283.08 nm f=0.0106 <S**2>=0.000
  170 -> 178  0.69037
  177 -> 180 -0.12356
Excited State 10: Singlet-A 4.5323 eV 273.55 nm f=0.0789 <S**2>=0.000
  169 -> 178 -0.19282
  170 -> 178  0.13514
  176 -> 179  0.12049
  177 -> 180  0.62915
  177 -> 181 -0.15256
Excited State 11: Singlet-A 4.6525 eV 266.49 nm f=0.0047 <S**2>=0.000
  169 -> 178  0.62600
  177 -> 180  0.14528
  177 -> 181 -0.18827
  177 -> 184 -0.12111
Excited State 12: Singlet-A 4.7037 eV 263.59 nm f=0.0065 <S**2>=0.000
  168 -> 178  0.66497
  177 -> 181 -0.16138
Excited State 13: Singlet-A 4.7277 eV 262.25 nm f=0.0345 <S**2>=0.000
  168 -> 178  0.21313
  169 -> 178  0.19485
  177 -> 180  0.20451
  177 -> 181  0.54492
  177 -> 183 -0.10355
  177 -> 184  0.17589
  177 -> 185  0.12619
Excited State 14: Singlet-A 4.7686 eV 260.00 nm f=0.0003 <S**2>=0.000
  167 -> 178  0.69624
Excited State 15: Singlet-A 4.8317 eV 256.61 nm f=0.0004 <S**2>=0.000
  166 -> 178  0.68421
Excited State 16: Singlet-A 4.8510 eV 255.58 nm f=0.0013 <S**2>=0.000
  166 -> 178 -0.11080
  176 -> 179  0.66443
  177 -> 180 -0.11440
Excited State 17: Singlet-A 4.8993 eV 253.07 nm f=0.0010 <S**2>=0.000
  165 -> 178  0.69408
Excited State 18: Singlet-A 4.9559 eV 250.18 nm f=0.0098 <S**2>=0.000
  161 -> 178  0.12503
  162 -> 178  0.34147
  163 -> 178  0.40172
  164 -> 178  0.44388
Excited State 19: Singlet-A 5.0321 eV 246.39 nm f=0.0205 <S**2>=0.000
  162 -> 178 -0.13210
  163 -> 178 -0.37308
  164 -> 178  0.45367
  177 -> 181  0.13777
  177 -> 182  0.11375
  177 -> 183  0.19721
  177 -> 184 -0.17384
  177 -> 185 -0.13077
Excited State 20: Singlet-A 5.0385 eV 246.07 nm f=0.0293 <S**2>=0.000
  161 -> 178 -0.11605
  163 -> 178  0.23852
  164 -> 178 -0.25227
  177 -> 181  0.25157
  177 -> 182  0.18397
  177 -> 183  0.32573
  177 -> 184 -0.28641
  177 -> 185 -0.21969
Excited State 21: Singlet-A 5.0750 eV 244.30 nm f=0.0035 <S**2>=0.000
  162 -> 178  0.57242
  163 -> 178 -0.36583
  164 -> 178 -0.13322
Excited State 22: Singlet-A 5.1360 eV 241.40 nm f=0.0007 <S**2>=0.000
  161 -> 178  0.66970
  162 -> 178 -0.12445
Excited State 23: Singlet-A 5.1618 eV 240.20 nm f=0.0097 <S**2>=0.000
  175 -> 179  0.55260
  177 -> 183  0.19448
  177 -> 184  0.28072
  177 -> 186 -0.17877

```

```

Excited State 24: Singlet-A 5.1946 eV 238.68 nm f=0.0005 <S**2>=0.000
  175 -> 179   -0.34005
  177 -> 182   0.34022
  177 -> 183   0.16752
  177 -> 184   0.41579
  177 -> 186   -0.19517

Excited State 25: Singlet-A 5.2223 eV 237.41 nm f=0.0010 <S**2>=0.000
  158 -> 178   -0.15934
  160 -> 178   0.66542

Excited State 26: Singlet-A 5.2342 eV 236.87 nm f=0.0037 <S**2>=0.000
  175 -> 179   0.20927
  177 -> 182   0.55027
  177 -> 183   -0.35613

Excited State 27: Singlet-A 5.2769 eV 234.96 nm f=0.0045 <S**2>=0.000
  177 -> 182   0.12785
  177 -> 183   0.34521
  177 -> 185   0.53086
  177 -> 186   0.23600

Excited State 28: Singlet-A 5.3463 eV 231.90 nm f=0.0071 <S**2>=0.000
  158 -> 178   -0.12754
  159 -> 178   0.67236
  160 -> 178   -0.11587

Excited State 29: Singlet-A 5.3993 eV 229.63 nm f=0.0006 <S**2>=0.000
  158 -> 178   0.44861
  160 -> 178   0.10843
  177 -> 184   -0.16599
  177 -> 185   0.22850
  177 -> 186   -0.42186

Excited State 30: Singlet-A 5.4132 eV 229.04 nm f=0.0164 <S**2>=0.000
  158 -> 178   0.45430
  160 -> 178   0.10047
  174 -> 179   0.27600
  177 -> 184   0.16239
  177 -> 185   -0.14538
  177 -> 186   0.34912

Excited State 31: Singlet-A 5.4242 eV 228.57 nm f=0.0052 <S**2>=0.000
  158 -> 178   -0.18955
  174 -> 179   0.60294
  177 -> 185   0.14357
  177 -> 186   -0.17606

Excited State 32: Singlet-A 5.4979 eV 225.51 nm f=0.0078 <S**2>=0.000
  157 -> 178   0.69062

```

JOB: ti552B2conf3TD2

Table S7. Transition Energy, Wavelength, and Oscillator Strengths of the Electronic Transition of **4b_{opt}** Calculated at the TD-B3LYP-D3/B1 [hexane] Level of Theory (The 177th orbital is Highest Occupied $\pi(\text{Si}=\text{Si})$ Orbital Shown in Figure S36.)

```

Excited State 1: Singlet-A 2.2988 eV 539.35 nm f=0.3119 <S**2>=0.000
  177 -> 178   0.70340
  177 <- 178   -0.10341

Excited State 2: Singlet-A 3.1749 eV 390.51 nm f=0.0023 <S**2>=0.000
  176 -> 178   0.70140

Excited State 3: Singlet-A 3.3693 eV 367.99 nm f=0.1086 <S**2>=0.000
  177 -> 179   0.69037

Excited State 4: Singlet-A 3.5986 eV 344.54 nm f=0.0201 <S**2>=0.000
  175 -> 178   0.69622

Excited State 5: Singlet-A 3.8080 eV 325.59 nm f=0.0016 <S**2>=0.000
  173 -> 178   0.16291
  174 -> 178   0.67317

Excited State 6: Singlet-A 3.9283 eV 315.61 nm f=0.0013 <S**2>=0.000
  172 -> 178   -0.13988
  173 -> 178   0.65972
  174 -> 178   -0.15412

Excited State 7: Singlet-A 4.1418 eV 299.35 nm f=0.0001 <S**2>=0.000
  171 -> 178   -0.37689
  172 -> 178   0.61608
  173 -> 178   0.11272

Excited State 8: Singlet-A 4.1854 eV 296.23 nm f=0.0724 <S**2>=0.000
  177 -> 180   0.67055

Excited State 9: Singlet-A 4.3874 eV 282.59 nm f=0.0249 <S**2>=0.000
  171 -> 178   0.63610
  172 -> 178   0.28142

Excited State 10: Singlet-A 4.5938 eV 269.89 nm f=0.0001 <S**2>=0.000
  170 -> 178   0.69429
  176 -> 179   -0.10165

Excited State 11: Singlet-A 4.6792 eV 264.97 nm f=0.0813 <S**2>=0.000
  169 -> 178   -0.14114
  174 -> 179   0.10548
  176 -> 179   0.52707
  177 -> 181   0.36617

Excited State 12: Singlet-A 4.7253 eV 262.38 nm f=0.0405 <S**2>=0.000
  176 -> 179   -0.35174
  177 -> 180   -0.11459
  177 -> 181   0.58229

Excited State 13: Singlet-A 4.9026 eV 252.89 nm f=0.0090 <S**2>=0.000
  169 -> 178   0.68026
  176 -> 179   0.14878

```

Excited State 14: Singlet-A 4.9725 eV 249.34 nm f=0.0033 <S**2>=0.000
 167 -> 178 -0.31898
 168 -> 178 0.61691
 Excited State 15: Singlet-A 5.0054 eV 247.70 nm f=0.0029 <S**2>=0.000
 166 -> 178 -0.10891
 167 -> 178 0.60489
 168 -> 178 0.30998
 Excited State 16: Singlet-A 5.0261 eV 246.68 nm f=0.0168 <S**2>=0.000
 166 -> 178 -0.10553
 174 -> 179 -0.12651
 175 -> 179 0.54060
 176 -> 179 0.14485
 177 -> 182 -0.15984
 177 -> 183 0.26132
 177 -> 184 0.14055
 Excited State 17: Singlet-A 5.0488 eV 245.57 nm f=0.0169 <S**2>=0.000
 167 -> 178 0.10951
 175 -> 179 -0.34584
 177 -> 182 -0.32851
 177 -> 183 0.38240
 177 -> 184 0.25802
 177 -> 186 -0.10046
 Excited State 18: Singlet-A 5.0851 eV 243.82 nm f=0.0088 <S**2>=0.000
 166 -> 178 -0.11153
 177 -> 182 0.55342
 177 -> 183 0.18614
 177 -> 184 0.51629
 177 -> 185 -0.11418
 Excited State 19: Singlet-A 5.1061 eV 242.82 nm f=0.0018 <S**2>=0.000
 163 -> 178 0.10417
 164 -> 178 0.14410
 165 -> 178 0.29054
 166 -> 178 0.57074
 175 -> 179 0.10469
 177 -> 182 0.11369
 177 -> 183 0.10819
 Excited State 20: Singlet-A 5.1409 eV 241.17 nm f=0.0011 <S**2>=0.000
 164 -> 178 0.30628
 165 -> 178 0.49870
 166 -> 178 -0.35547
 Excited State 21: Singlet-A 5.1824 eV 239.24 nm f=0.0131 <S**2>=0.000
 162 -> 178 0.11872
 164 -> 178 0.14626
 177 -> 182 -0.12901
 177 -> 183 -0.43451
 177 -> 184 0.46035
 177 -> 185 -0.10482
 Excited State 22: Singlet-A 5.1936 eV 238.73 nm f=0.0056 <S**2>=0.000
 162 -> 178 0.40086
 163 -> 178 -0.29081
 164 -> 178 0.38274
 165 -> 178 -0.22652
 177 -> 183 0.14759
 177 -> 184 -0.15030
 Excited State 23: Singlet-A 5.2612 eV 235.66 nm f=0.0015 <S**2>=0.000
 162 -> 178 -0.29460
 163 -> 178 0.36509
 164 -> 178 0.43185
 165 -> 178 -0.29055
 Excited State 24: Singlet-A 5.2980 eV 234.02 nm f=0.0151 <S**2>=0.000
 162 -> 178 -0.11196
 163 -> 178 -0.25183
 172 -> 179 0.12206
 173 -> 179 -0.12880
 174 -> 179 0.54284
 175 -> 179 0.13774
 177 -> 185 0.15664
 Excited State 25: Singlet-A 5.2984 eV 234.00 nm f=0.0088 <S**2>=0.000
 162 -> 178 0.44875
 163 -> 178 0.42927
 164 -> 178 -0.15675
 165 -> 178 -0.16161
 174 -> 179 0.19478
 Excited State 26: Singlet-A 5.3361 eV 232.35 nm f=0.0053 <S**2>=0.000
 161 -> 178 -0.16074
 174 -> 179 -0.23032
 177 -> 184 0.15844
 177 -> 185 0.58371
 177 -> 187 0.16239
 Excited State 27: Singlet-A 5.3620 eV 231.23 nm f=0.0047 <S**2>=0.000
 161 -> 178 0.66760
 177 -> 185 0.14084
 Excited State 28: Singlet-A 5.4234 eV 228.61 nm f=0.0150 <S**2>=0.000
 160 -> 178 0.14152
 161 -> 178 0.11250
 172 -> 179 -0.25415
 173 -> 179 0.54395
 174 -> 179 0.17740
 176 -> 180 -0.10709
 177 -> 185 0.11566
 Excited State 29: Singlet-A 5.4528 eV 227.38 nm f=0.0132 <S**2>=0.000
 173 -> 179 -0.10373
 177 -> 184 0.13771
 177 -> 185 0.10931
 177 -> 186 0.54331
 177 -> 187 -0.32740
 Excited State 30: Singlet-A 5.4621 eV 226.99 nm f=0.0014 <S**2>=0.000
 158 -> 178 -0.16886
 160 -> 178 0.64203
 173 -> 179 -0.12936
 177 -> 186 -0.12461
 Excited State 31: Singlet-A 5.5171 eV 224.73 nm f=0.0090 <S**2>=0.000
 177 -> 182 -0.10751
 177 -> 185 -0.17647
 177 -> 186 0.30644
 177 -> 187 0.45194
 177 -> 188 0.22287
 177 -> 189 0.21079
 177 -> 190 0.16525
 177 -> 191 -0.10689
 Excited State 32: Singlet-A 5.5993 eV 221.43 nm f=0.0023 <S**2>=0.000
 159 -> 178 0.52163

171 -> 179 0.13480
 172 -> 179 -0.35329
 173 -> 179 -0.19564

JOB: ti552B2conf1TD2

Table S8. Transition Energy, Wavelength, and Oscillator Strengths of the Electronic Transition of 5_{opt} Calculated at the TD-B3LYP-D3/B1 [hexane] Level of Theory (The 151st orbital is Highest Occupied $\pi(\text{Si}=\text{Si})$ Orbital Shown in Figure S36.)

Excited State 1:	Singlet-A	2.1140 eV	586.49 nm	f=0.0058 <S**2>=0.000
197 -> 198	0.69358			
197 -> 199	-0.12987			
This state is for optimization and/or second-order correction.				
Total Energy, E(TD-HF/TD-KS) = -3501.15742787				
Copying the excited state density for this state as the 1-particle RhoCI density.				
Excited State 2:	Singlet-A	2.4609 eV	503.82 nm	f=0.0715 <S**2>=0.000
197 -> 198	0.12198			
197 -> 199	0.68452			
197 -> 200	-0.12089			
Excited State 3:	Singlet-A	3.0666 eV	404.30 nm	f=0.2108 <S**2>=0.000
197 -> 199	0.18605			
197 -> 200	0.67424			
197 -> 202	0.13396			
Excited State 4:	Singlet-A	3.5937 eV	345.01 nm	f=0.0583 <S**2>=0.000
196 -> 198	0.16015			
197 -> 200	-0.18923			
197 -> 202	0.66304			
Excited State 5:	Singlet-A	3.7123 eV	333.98 nm	f=0.1718 <S**2>=0.000
196 -> 198	0.66906			
197 -> 202	-0.14751			
Excited State 6:	Singlet-A	3.8748 eV	319.97 nm	f=0.0061 <S**2>=0.000
196 -> 199	0.67941			
196 -> 200	0.15017			
Excited State 7:	Singlet-A	3.9476 eV	314.08 nm	f=0.0376 <S**2>=0.000
197 -> 201	0.68234			
197 -> 203	-0.15081			
Excited State 8:	Singlet-A	4.1234 eV	300.68 nm	f=0.0288 <S**2>=0.000
195 -> 198	0.52892			
195 -> 200	0.10165			
196 -> 199	-0.13298			
196 -> 200	0.39575			
Excited State 9:	Singlet-A	4.1683 eV	297.45 nm	f=0.0124 <S**2>=0.000
195 -> 198	-0.10991			
195 -> 199	-0.42995			
196 -> 200	0.52358			
Excited State 10:	Singlet-A	4.2977 eV	288.49 nm	f=0.0049 <S**2>=0.000
197 -> 201	0.14512			
197 -> 203	0.66656			
197 -> 204	0.10600			
Excited State 11:	Singlet-A	4.3420 eV	285.55 nm	f=0.0194 <S**2>=0.000
195 -> 199	-0.13304			
197 -> 203	-0.10726			
197 -> 204	0.51734			
197 -> 205	-0.36584			
197 -> 206	-0.14692			
Excited State 12:	Singlet-A	4.4096 eV	281.17 nm	f=0.0005 <S**2>=0.000
195 -> 199	-0.30784			
197 -> 204	0.27080			
197 -> 205	0.43283			
197 -> 206	0.32880			
Excited State 13:	Singlet-A	4.4125 eV	280.99 nm	f=0.0047 <S**2>=0.000
195 -> 199	0.56336			
195 -> 200	0.13361			
196 -> 200	-0.11727			
197 -> 204	0.30051			
197 -> 205	0.10992			
197 -> 206	0.14620			
Excited State 14:	Singlet-A	4.5238 eV	274.07 nm	f=0.0046 <S**2>=0.000
194 -> 198	0.63155			
195 -> 198	-0.11546			
195 -> 199	0.15233			
195 -> 200	-0.15831			
Excited State 15:	Singlet-A	4.5368 eV	273.29 nm	f=0.0087 <S**2>=0.000
194 -> 198	0.10993			
197 -> 204	-0.12245			
197 -> 205	-0.36957			
197 -> 206	0.55217			
Excited State 16:	Singlet-A	4.6767 eV	265.11 nm	f=0.0005 <S**2>=0.000
194 -> 198	0.19808			
194 -> 199	-0.23095			
195 -> 199	-0.10235			
195 -> 200	0.51865			
197 -> 204	0.11389			
197 -> 207	-0.14168			
197 -> 208	-0.12092			
197 -> 209	-0.19473			
197 -> 212	-0.11520			
Excited State 17:	Singlet-A	4.7159 eV	262.91 nm	f=0.0130 <S**2>=0.000
195 -> 199	-0.18621			
195 -> 200	0.00538			
197 -> 204	-0.11476			
197 -> 207	0.37131			
197 -> 208	0.22005			
197 -> 209	0.35151			

197 -> 211 -0.15333
 197 -> 212 0.13954
 Excited State 18: Singlet-A 4.8045 eV 258.06 nm f=0.0037 <S**2>=0.000
 197 -> 205 0.11253
 197 -> 207 0.46515
 197 -> 208 0.19301
 197 -> 209 -0.31258
 197 -> 211 0.24218
 197 -> 212 -0.20579
 197 -> 214 -0.11613
 Excited State 19: Singlet-A 4.8153 eV 257.48 nm f=0.0113 <S**2>=0.000
 197 -> 207 -0.27980
 197 -> 208 0.54063
 197 -> 210 0.24721
 197 -> 211 0.18314
 Excited State 20: Singlet-A 4.8402 eV 256.16 nm f=0.0018 <S**2>=0.000
 194 -> 199 0.62851
 195 -> 199 -0.12786
 195 -> 200 0.23781
 Excited State 21: Singlet-A 4.8738 eV 254.39 nm f=0.0367 <S**2>=0.000
 192 -> 198 -0.28834
 193 -> 198 0.57866
 193 -> 199 0.18999
 Excited State 22: Singlet-A 4.9506 eV 250.44 nm f=0.0198 <S**2>=0.000
 192 -> 199 0.35886
 193 -> 198 -0.13059
 193 -> 199 0.53231
 194 -> 199 -0.10076
 197 -> 212 0.10879
 Excited State 23: Singlet-A 4.9603 eV 249.95 nm f=0.0072 <S**2>=0.000
 197 -> 208 -0.21632
 197 -> 209 0.42314
 197 -> 210 0.19789
 197 -> 211 0.22127
 197 -> 212 -0.36541
 197 -> 213 -0.12152
 Excited State 24: Singlet-A 4.9838 eV 248.78 nm f=0.0022 <S**2>=0.000
 197 -> 208 -0.14566
 197 -> 211 0.45586
 197 -> 212 0.36576
 197 -> 213 0.28282
 Excited State 25: Singlet-A 5.0454 eV 245.74 nm f=0.3240 <S**2>=0.000
 192 -> 198 0.59862
 193 -> 198 0.29684
 197 -> 210 -0.10590
 Excited State 26: Singlet-A 5.0573 eV 245.16 nm f=0.0075 <S**2>=0.000
 192 -> 198 0.12329
 197 -> 207 0.12490
 197 -> 208 -0.13630
 197 -> 210 0.56827
 197 -> 211 -0.21441
 197 -> 212 0.19195
 197 -> 214 -0.14416
 Excited State 27: Singlet-A 5.1163 eV 242.33 nm f=0.0038 <S**2>=0.000
 191 -> 198 0.13238
 192 -> 199 0.36729
 193 -> 199 -0.19644
 193 -> 200 -0.13288
 194 -> 200 0.47823
 197 -> 212 -0.10056
 Excited State 28: Singlet-A 5.1586 eV 240.34 nm f=0.0174 <S**2>=0.000
 192 -> 199 -0.17224
 193 -> 199 0.11591
 197 -> 210 0.12575
 197 -> 212 -0.21174
 197 -> 213 0.50748
 197 -> 214 0.31054
 Excited State 29: Singlet-A 5.1631 eV 240.14 nm f=0.0018 <S**2>=0.000
 192 -> 199 -0.34128
 192 -> 200 -0.16000
 193 -> 199 0.19744
 193 -> 200 0.19734
 194 -> 200 -0.47837
 197 -> 213 -0.13122
 Excited State 30: Singlet-A 5.1753 eV 239.57 nm f=0.0124 <S**2>=0.000
 190 -> 198 -0.14763
 191 -> 198 0.66184
 194 -> 200 -0.11909
 Excited State 31: Singlet-A 5.2703 eV 235.25 nm f=0.0020 <S**2>=0.000
 196 -> 202 0.11010
 197 -> 210 0.14437
 197 -> 211 0.17744
 197 -> 212 0.12675
 197 -> 213 -0.29868
 197 -> 214 0.54246
 197 -> 217 -0.10251
 Excited State 32: Singlet-A 5.3287 eV 232.67 nm f=0.0119 <S**2>=0.000
 196 -> 202 0.39779
 197 -> 216 0.50316
 197 -> 219 -0.18118

JOB: ti552SiBDMAP_TD2

3. Temperature-Dependent UV-vis Spectrum of 4

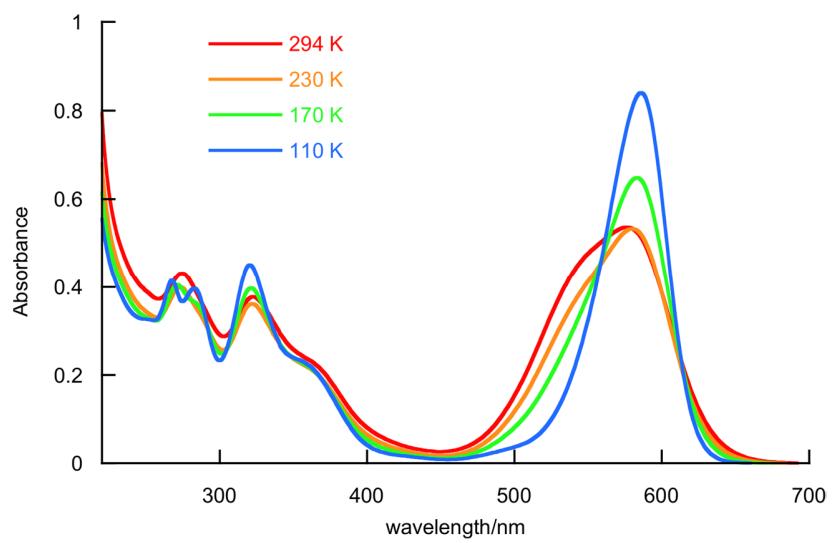


Figure S36. UV-vis absorption spectrum **4** at various temperatures in 3-methylpentane.